High-efficiency Transformerless PV Inverter Circuits

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ABSTRACT

With worldwide growing demand for electric energy, there has been a great interest in exploring photovoltaic (PV) sources. For the PV generation system, the power converter is the most essential part for the efficiency and function performance. In recent years, there have been quite a few new transformerless PV inverters topologies, which eliminate the traditional line frequency transformers to achieve lower cost and higher efficiency, and maintain lower leakage current as well.

With an overview of the state-of-the-art transformerless PV inverters, a new inverter technology is summarized in the Chapter 2, which is named V-NPC inverter technology. Based this V-NPC technology, a family of high efficiency transformerless inverters are proposed and detailly analyzed. The experimental results demonstrate the validity of V-NPC technology and high performance of the transformerless inverters.

For the lower power level transformerless inverters, most of the innovative topologies try to use super junction metal oxide semiconductor field effect transistor (MOSFET) to boost efficiency, but these MOSFET based inverter topologies suffer from one or more of these drawbacks: MOSFET failure risk
from body diode reverse recovery, increased conduction losses due to more devices, or low magnetics utilization. By splitting the conventional MOSFET based phase leg with an optimized inductor, Chapter 3 proposes a novel MOSFET based phase leg configuration to minimize these drawbacks. Based on the proposed phase leg configuration, a high efficiency single-phase MOSFET transformerless inverter is presented for the PV micro-inverter applications. The PWM modulation and circuit operation principle are then described. The common mode and differential mode voltage model is then presented and analyzed for circuit design. Experimental results of a 250 W hardware prototype are shown to demonstrate the merits of the proposed MOSFET based phase-le and the proposed transformerless inverter.

New codes require PV inverters to provide system regulation and service to improve the distribution system stabilization. One obvious impact on PV inverters is that they now need to have reactive power generation capability. The Chapter 4 improves the MOFET based transformerless inverter in the Chapter 3 and proposed a novel pulse width modulation (PWM) method for reactive power generation. The ground loop voltage of this inverter under the proposed PWM method is also derived with common mode and differential mode circuit analyses, which indicate that high-frequency voltage component can be minimized with symmetrical design of inductors. A 250-W inverter hardware prototype has been designed and fabricated. Steady state and transient operating conditions are tested to demonstrate the validity of
improved inverter and proposed PWM method for reactive power generation, high efficiency of the inverter circuit, and the high-frequency-free ground loop voltage.

Besides the high efficiency inverter circuit, the grid connection function is also the essential part of the PV system. The Chapter 5 present the overall function blocks for a grid-connected PV inverter system. The current control and voltage control loop is then analyzed, modeled, and designed. The dynamic reactive power generation is also realized in the control system. The new PLL method for the grid frequency/voltage disturbance is also realized and demonstrate the validity of the detection and protection capability for the voltage/frequency disturbance.

At last, a brief conclusion is given in the Chapter 6 about each work. After that, future works on device packaging, system integration, innovation on inverter circuit, and standard compliance are discussed.
To my parents
Mingbing Chen
Dimei Xu
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_Baifeng Chen_

_07/07/2015 in Blacksburg_
CONTENTS

CHAPTER 1 INTRODUCTION ................................................................. 1
  1.1 Research background and motivations ........................................... 1
  1.2 State-of-the-art PV inverters ....................................................... 5
    1.2.1 Microinverter ............................................................... 5
    1.2.2 String inverter ............................................................. 6
    1.2.3 Central inverter ............................................................ 6
  1.3 State-of-the-art PV system structures ........................................... 6
    1.3.1 Two-stage system with high frequency transformer and pseudo DC link .................................................. 6
    1.3.2 Two-stage system with high frequency transformer and DC link bus voltage ............................................. 7
    1.3.3 Two-stage system with non-isolated DC-DC and DC link bus voltage ......................................................... 8
    1.3.4 Single-stage system with line frequency transformer ................. 8
    1.3.5 Single-stage system without isolation transformer ..................... 9
  1.4 Objectives of the research project ............................................. 10
  1.5 Outline of the dissertation ..................................................... 12

CHAPTER 2 TRANSFORMERLESS INVERTER CIRCUITS WITH
ADVANCED NEUTRAL POINT CLAMPING TECHNOLOGY ............ 15
  2.1 Introduction .................................................................................. 15
  2.2 State-of-the-art transformerless inverters ..................................... 17
  2.3 Neutral point virtually clamped (V-NPC) technology with
    auxiliary freewheeling switches .................................................... 26
  2.4 A family of high-efficiency transformerless inverter circuits
    with V-NPC Technology ................................................................. 30
    2.4.1 Proposed inverter topologies ............................................... 31
    2.4.2 PWM method and working principle .................................... 33
    2.4.3 Efficiency calculation and loss analysis ................................ 41
    2.4.4 Experimental Results .......................................................... 47
  2.5 Inverter circuits with improved V-NPC technology for high input
    DC voltage application .................................................................. 52
    2.5.1 Single-phase full bridge NPC inverter .................................. 52
    2.5.2 Inverter circuit with V-NPC method ..................................... 55
    2.5.3 A family of inverter circuits with improved V-NPC method .... 56
  2.6 Summary ..................................................................................... 59

CHAPTER 3 MOSFET BASED TRANSFORMERLESS INVERTER
CIRCUIT WITH HIGH MAGNETIC UTILIZATION ....................... 60
  3.1 Introduction ............................................................................... 60
  3.2 State-of-the-art MOSFET based transformerless inverters .......... 61
    3.2.1 Transformerless inverter with MOSFET phase-leg ................ 61

viii
CHAPTER 4 REACTIVE POWER GENERATION ON MOSFET BASED TRANSFORMERLESS INVERTER ........................................... 93
 4.1 INTRODUCTION ................................................................. 93
 4.2 REACTIVE POWER CAPABILITY FOR CURRENT MOSFET BASED TRANSFORMERLESS INVERTERS ................................................................. 96
    4.2.1 High efficiency topologies suffer from MOSFET body diode reverse recovery for reactive power generation ................................................................. 97
    4.2.2 High efficiency MOSFET inverters don’t support reactive power generation ................................................................. 98
    4.2.3 MOSFET inverter support reactive power generation ................................................................. 99
    4.2.4 A improved MOSFET inverter for reactive power generation ................................................................. 100
 4.3 OPERATING MODES OF THE IMPROVED MOSFET BASED TRANSFORMERLESS INVERTERS ................................................................. 102
 4.4 PWM METHOD AND REALIZATION FOR IMPROVED MOSFET INVERTER ................................................................. 106
 4.5 GROUND LOOP VOLTAGE ANALYSIS UNDER REACTIVE POWER GENERATION ................................................................. 114
 4.6 EXPERIMENTAL RESULTS ................................................................. 118
 4.7 SUMMARY ........................................................................... 124
CHAPTER 5 GRID CONNECTION ANALYSIS AND DESIGN .............. 126
 5.1 INTRODUCTION ................................................................. 126
 5.2 SYSTEM CONTROL AND MODELING ................................................................. 127
    5.2.1 Current loop modeling and control ................................................................. 128
    5.2.2 DC voltage loop modeling and control ................................................................. 136
 5.3 DYNAMIC REACTIVE POWER GENERATION ................................................................. 141
 5.4 A NOVEL PLL FOR GRID VOLTAGE/FREQUENCY DISTURBANCE ................................................................. 146
    5.4.1 Traditional PLL method ................................................................. 146
    5.4.2 Improved PLL method ................................................................. 149
    5.4.3 Voltage magnitude detection method ................................................................. 153
 5.5 SUMMARY ........................................................................... 156
CHAPTER 6 CONCLUSIONS AND FUTURE WORK .................... 158
 6.1 CONCLUSIONS ........................................................................... 158
 6.2 FUTURE WORK ........................................................................... 160
LIST OF PUBLICATIONS ................................................................. 162
REFERENCE .................................................................................. 167
LIST OF FIGURES

Figure 1.1 Microinverter, string inverter, and central inverter..........................5
Figure 1.2 Two-stage system with high frequency transformer and pseudo DC link.............................................................................................................................7
Figure 1.3 Two-stage system with high frequency transformer and DC link bus voltage......................................................................................................................8
Figure 1.4 Two-stage system with non-isolated DC-DC and DC link bus voltage......................................................................................................................8
Figure 1.5 Single-stage system with line frequency transformer ......................9
Figure 1.6 Single-stage system without isolation transformer........................10
Figure 2.1 PV inverter system with transformer...........................................15
Figure 2.2 The transformerless PV inverter system ......................................16
Figure 2.3 Transformerless inverter system with parasitic capacitance............16
Figure 2.4 Neutral point clamp (NPC) inverter ............................................18
Figure 2.5 T-type NPC inverter .....................................................................19
Figure 2.6 Improved NPC inverter topology ...............................................19
Figure 2.7 The single phase H-bridge inverter .............................................21
Figure 2.8 The HERIC inverter with paralleled auxiliary freewheeling switches .................................................................22
Figure 2.9 The HERIC inverter topology with back-to-back auxiliary freewheeling switches ..................................................................................................23
Figure 2.10 The H5TM inverter topology .......................................................24
Figure 2.11 The H6 inverter topology .............................................................25
Figure 2.12 The symmetrical H6 inverter topology .......................................25
Figure 2.13 The hybrid phase leg inverter topology .......................................26
Figure 2.14 Current freewheeling path for NPC inverter ...............................27
Figure 2.15 Current freewheeling path for T-type inverter .............................27
Figure 2.16 Current freewheeling path of HERIC inverter ............................28
Figure 2.17 Current freewheeling path of H6 inverter ...................................28
Figure 2.18 Current freewheeling path of H5 inverter ...................................29
Figure 2.19 Current freewheeling path of symmetrical H6 inverter ...............29
Figure 2.20 Current freewheeling path of the hybrid phase leg inverter...........30
Figure 2.21 Proposed a family of transformerless inverters ..........................33
Figure 2.22 PWM implemented circuit for the proposed inverter .................34
Figure 2.23 The unipolar modulation gating signals for proposed inverter ..34
Figure 2.24 Operating modes of the proposed transformerless inverter

   Topology 1 in Figure 2.21(a): (a) Positive half-line cycle, S1 and S4 are on, (b) Positive half-line cycle, S1 and S4 are off, free-wheeling current goes through S5 and S6, (c) Negative half-line cycle, S3 and S2 are on, (d) Negative half-line cycle, S3 and S2 are off, freewheeling current goes through S5 and S6.................................................................36

Figure 2.25 Operating modes of the inverter 3 in Figure 2.21(c): (a) Positive half-line cycle, S1 and S4 are on, (b) Positive half-line cycle, S1 and S4 are
off, free-wheeling current goes through S₅ and D₅. (c) Negative half-line
cycle, S₃ and S₂ are on, (d) Negative half-line cycle, S₃ and S₂ are off,
freewheeling current goes through D₆ and S₆.

Figure 2.26 Simulation results of: (I) Topology 1 in Figure 2.21 (a); (II)
Topology 3 in Figure 2.21 (c).

Figure 2.27 Calculated individual power loss under different power levels.

Figure 2.28 Calculated total loss and efficiency under different power levels.

Figure 2.29 250W micro-inverter hardware prototype.

Figure 2.30 PWM gate signals waveforms for proposed inverter.

Figure 2.31 Output voltage/ current and ground loop voltage waveforms.

Figure 2.32 The equivalent ground loop in proposed inverter topology 1 in
Fig. 21(a).

Figure 2.33 Simulation results of ground loop voltage V_EG in proposed
inverter topology 1 in Fig. 21(a).

Figure 2.34 Calculated and test efficiency results under different power
levels.

Figure 2.35 The half bridge NPC inverter.

Figure 2.36 The single-phase full bridge NPC inverter.

Figure 2.37 The PWM implementation method and gating signals for single-
phase full bridge NPC inverter.

Figure 2.38 Operating modes of single-phase full bridge NPC inverter.

Figure 2.39 NPC single-phase full bridge inverter with V-NPC method.

Figure 2.40 Operating modes of V-NPC based single-phase full bridge
inverter.

Figure 2.41 A family of single-phase full bridge inverters based on improved
V-NPC technology.

Figure 2.42 The output voltage, output current, and drain source voltage of
devices.

Figure 3.1 (a) Complimentary phase-leg with CoolMOS; (b) Buck converter
with CoolMOS and SiC diode.

Figure 3.2 The two stage topology with pseudo DC link.

Figure 3.3 Dual buck transformerless inverter.

Figure 3.4 Bidirectional dual buck inverter.

Figure 3.5 MOSFET phase leg configurations: (a) Traditional phase leg, (b)
Dual buck method, (c) Proposed method.

Figure 3.6 Double pulse test of the body diode reverse recovery.

Figure 3.7 Diode reverse recovery of IPB60R099C6 in (a) traditional phase
leg (b) proposed phase leg.

Figure 3.8 Proposed transformerless inverter topology with (a) separated
magnetics (b) integrated magnetics.

Figure 3.9 PWM implemented circuit for the proposed inverter.
Figure 3.10  PWM signals in time domain for the proposed inverter ............71
Figure 3.11  Operating modes of the proposed transformerless inverter: (a) Positive half-line cycle, S₁ and S₄ are on, (b) Positive half-line cycle, S₁ and S₄ are off, free-wheeling current goes through S₅ and D₅, (c) Negative half-line cycle, S₃ and S₂ are on, (d) Negative half-line cycle, S₃ and S₂ are off, free-wheeling current goes through S₆ and D₆..............................73
Figure 3.12  The inverter system with ground loop parasitic capacitor .......75
Figure 3.13  Equivalent circuit with CM and DM model for the positive half-line cycle ..................................................................................75
Figure 3.14  Equivalent circuit with CM and DM model for the negative half-line cycle ..................................................................................77
Figure 3.15  Calculated individual power loss under different power levels..84
Figure 3.16  Calculated total loss and efficiency under different power levels. ...............................................................................................84
Figure 3.17  250W two stage non-isolated micro-inverter hardware prototype. ..................................................................................................85
Figure 3.18  Output voltage and current waveforms..................................86
Figure 3.19  PWM gate signals waveforms..............................................86
Figure 3.20  Inverter splitting inductor current waveform.........................87
Figure 3.21  Waveforms of Voltage between grid ground and DC ground (V repreh) ..........................................................................................87
Figure 3.22  Efficiency test results of 250W proposed inverter. .................88
(a) NPC topology (b) NPC topology with proposed phase-leg ............89
Figure 3.23  Application of proposed MOSFET phase-leg on NPC topology ..89
(a) T-type inverter topology (b) T-type inverter topology with proposed phase-leg ...........................................................................................90
Figure 3.24  Application of proposed MOSFET phase-leg on T-type inverter 90
(a) H-bridge topology (b) H-bridge topology with proposed phase-leg ...........................................................................................90
Figure 3.25  Application of proposed MOSFET phase-leg on H-bridge topology ...............................................................................................90
(a) H₅ topology (b) H₅ topology with proposed phase-leg ............90
Figure 3.26  Application of proposed MOSFET phase-leg on H₅ topology ....90
(a) H₆ topology (b) H₆ topology with proposed phase-leg ............91
Figure 3.27  Application of proposed MOSFET phase-leg on H₆ topology ....91
(a) Asymmetry H₆ topology (b) Asymmetry H₆ topology with proposed phase-leg .................................................................91
Figure 3.28  Application of proposed MOSFET phase-leg on asymmetry H₆ topology ...........................................................................................91
Figure 4.1  Power line voltage distribution in PV generation system with/without reaction power compensation of PV inverters ..................93
Figure 4.2  Four different regions in time domain under current lagging condition ...............................................................................................95
Figure 4.3 MOSFET phase leg configurations: (a) Traditional phase-leg method, (b) unidirectional buck method, (c) Bidirectional buck method. 97
Figure 4.4 High efficiency transformerless inverter suffer MOSFET body diode reverse recovery for reactive power generation ......................................98
Figure 4.5 High efficiency transformerless inverter don’t support reactive power generation .........................................................................................99
Figure 4.6 MOSFET based inverter support reactive power generation.....100
Figure 4.7 MOSFET based Phase-leg method .............................................101
Figure 4.8 Improved CoolMOS/SiC-diode based transformerless inverter..101
Figure 4.9 Buck operating mode in the I region ........................................103
Figure 4.10 Boost operating mode in the II region .................................104
Figure 4.11 Buck operating mode in the III region .................................105
Figure 4.12 Boost operating mode in the IV region .................................105
Figure 4.13 Control system for voltage reference generation ...............107
Figure 4.14 Individual duty cycle generation and PWM modulation method ........................................................................................................107
Figure 4.15 Corresponding codes in DSP for duty cycle generator modules109
Figure 4.16 Gating signals of S_1, S_4, S_5, S_2/ S_3, and S_6 for unity power factor condition .................................................................111
Figure 4.17 Gating signals of S_1, S_4, S_5, S_2/ S_3, and S_6 for current leading condition .................................................................112
Figure 4.18 Gating signals of S_1, S_4, S_5, S_2/ S_3, and S_6 for current lagging condition .................................................................113
Figure 4.19 The inverter system with ground loop parasitic capacitor ......114
Figure 4.20 Equivalent circuit with CM and DM model in region II ........115
Figure 4.21 Equivalent circuit with CM and DM model in region IV .......116
Figure 4.22 250W micro-inverter hardware prototype .........................118
Figure 4.23 The PWM gating signals for unity power factor (PF=1) operation .....................................................................................................119
Figure 4.24 The PWM gating signals for current leading (PF=0.7) operation .................................................................................................119
Figure 4.25 The PWM gating signals for current lagging (PF=0.7) operation .................................................................................................120
Figure 4.26 Voltage and current under PF=1 ........................................121
Figure 4.27 Voltage and current under PF=0.7 .....................................122
Figure 4.28 Voltage and current under PF=0.7 .....................................122
Figure 4.29 Ground loop leakage current waveform ..........................123
Figure 4.30 Efficiency test results of proposed transformerless inverter ....124
Figure 5.1 Block diagram of a typical grid-connected inverter system ........126
Figure 5.2 Block diagram of a simplified control system ........................127
Figure 5.3 Simplified current control system ........................................128
Figure 5.4 Bode diagram of second-order low-pass filter .....................129
Figure 5.5 Bode diagram of the G_m(s) ..................................................130
Figure 5.6 Bode diagram of the F_m(s) ..................................................131
Figure 5.8  Bode diagram of current control loop plant $G_{open_{-}di}(s)$ ........................................133
Figure 5.9  Bode diagram of current controller $G_{c_{-}i}(s)$ .................................................................134
Figure 5.10  Bode diagram of current control open loop $G_{open_{-}u}(s)$ ....................................................134
Figure 5.11  Bode diagram of current control close loop $G_{close_{-}u}(s)$ ..................................................135
Figure 5.13  Bode diagram of voltage loop plant $G_{open_{-}iv}(s)$ ...............................................................137
Figure 5.14  Nyquist plot of voltage loop plant $G_{open_{-}iv}(s)$ .................................................................138
Figure 5.15  Bode diagram of voltage control open loop $G_{open_{-}vv}(s)$ ...................................................139
Figure 5.16  Nyquist plot of voltage control open loop $G_{open_{-}vv}(s)$ for wide frequency range .................................................................139
Figure 5.17  Nyquist plot of voltage control open loop $G_{open_{-}vv}(s)$ for low frequency range .................................................................140
Figure 5.18  DC bus voltage is control from 370 to 400 Vdc .................................................................141
Figure 5.19  the steady state waveform for ac current/voltage and dc voltage .................................................................141
Figure 5.20  Voltage-Var control with dead-band method .................................................................143
Figure 5.21  Voltage-Var control with hysteresis method .................................................................143
Figure 5.22  System block diagram of Voltage-Var control .................................................................144
Figure 5.23  Transient form unity power factor (PF=1) operation to reactive power generation (PF=0.7) operation .................................................................145
Figure 5.24  Transient form unity power factor (PF=1) operation to reactive power absorbing (PF=0.7) operation .................................................................146
Figure 5.25  Block diagram of the traditional PLL module .................................................................147
Figure 5.26  Simulation results of traditional PLL method .................................................................148
Figure 5.27  Frequency detection results of traditional PLL .................................................................148
Figure 5.28  Block diagram of the improved PLL module .................................................................149
Figure 5.29  The block diagram of notch filter .................................................................150
Figure 5.30  Frequency detection results of improved PLL .................................................................150
Figure 5.31  Experimental abnormal over-frequency trip .................................................................151
Figure 5.32  Experimental abnormal under-frequency trip .................................................................151
Figure 5.33  Abnormal over-frequency test .................................................................152
Figure 5.34  Abnormal under-frequency test .................................................................152
Figure 5.35  Voltage magnitude detection method .................................................................153
Figure 5.36  Under-voltage (88%) test result .................................................................154
Figure 5.37  Under-voltage (50%) test result .................................................................154
Figure 5.38  Over-voltage (110%) test result .................................................................155
Figure 5.39  Over-voltage (120%) test result .................................................................155
LIST OF TABLES

Table 5-1 Summary of abnormal frequency test results .........................153
Table 5-2 Summary of abnormal voltage test results ..........................156
Chapter 1 Introduction

1.1 Research background and motivations

Solar energy offers a number of strategic benefits to all the world. Replacing fossil-fuel combustion with solar energy reduces emissions of human-induced greenhouse gases (GHGs) and air pollutants. Sunlight is a free resource, thus, once solar technologies are installed, they have very low operating costs and require minimal non-solar inputs—this provides insurance against conventional fuel supply disruptions and price volatility. In addition, growing the domestic solar energy industry could establish the solar-related industry, and support a growing number of solar-related jobs [1].

Despite these benefits, solar energy currently supplies only a small fraction of U.S. energy needs. The SunShot Initiative, Launched in 2011 by U.S. Department of Energy (DOE), is aiming at paving the way for rapid, large-scale adoption of solar electricity across the United States through research and development (R&D) and partly through U.S. and global solar market stimulation. The target is using solar energy to satisfy roughly 14% of U.S. electricity demand by 2030 and 27% by 2050 [1-4].

A typical solar power generation system feature three components: balance-of-systems that support all the system, PV modules that consist of multiple PV cells, and power electronic converter that connect the PV cells to the power grid.
Balance-of-systems include support structures, mounting hardware, wiring, monitoring equipment, shipping, and lands. Balance-of-systems also include system design and engineering, customer and site acquisition, installation, permitting, interconnection and inspection, financing, contracting, market-regulatory barriers, and operation and maintenance[5],[6].

PV modules consist of interconnected PV cells which are fabricated from semiconductor materials and can converter sunlight into electricity based on the photoelectric effect. Crystalline silicon based PV modules, which can be divided as monocrystalline and multicrystalline silicon technology, constitute about 85% of the current PV market. The rated DC efficiencies of standard crystalline silicon PV modules are about 14%–16%. A number of non-standard cell architectures—such as back-contact cells—are growing because they offer the potential for significantly higher efficiency. Thin-film PV cells, which made from a few microns thickness bandgap semiconductor, have the benefit of low cost and low volume due to thickness is 100 times thinner than crystalline silicon cells. Thin-film modules have lower DC efficiencies than crystalline silicon modules: about 9%–12% for cadmium telluride (CdTe), 6%–9% for amorphous silicon (a-Si), and 8%–14% for alloys of copper indium gallium diselenide (CIGS). CdTe-based thin-film modules has experienced significantly higher maker growth during the last decade due to lower-cost and non-vacuum characteristics. Glass is a common substrate/superstrate, but thin films can
also be deposited on flexible substrates/superstrates such as metal, which allows for the potential for flexible lightweight solar modules. Eliminating the need for glass through the use of “ultra-barrier” flexible glass replacement materials is an important next step in thin film development [1-6].

Power electronic converter is the heart of every PV plant, which is an environmentally power generation system that uses the PV cells to convert sunlight into electrical power. The main task of a PV inverter is to convert direct current into alternating current to fit with the public power distribution grids. As there is a bottleneck for the PV cell energy conversion efficiency, PV inverters is required to have high efficiency for the maximum solar energy utilization. High efficiency is also required by PV inverter system’s reliable operation, PV plants are designed to operate for at least twenty years, so failure possibility from thermal can be reduced with high efficiency power conversion. High efficiency is also required by PV inverter system for the low cost and low volume design, high efficiency and high switching frequency power electronics system can reduce the passive component and cooling component. For custom, high efficiency PV inverter means more PV power generation and fast return of capital investment [7-13].

Besides the high efficiency performance of PV power electronics system, the advanced functions is also the key of all the PV plant. The PV inverter need collect data on the energy yields of the PV plant, monitors the electrical activity of the PV array and signals, and also need monitor the power distribution grid.
If the grid voltage and frequencies overcome the specified limiting, PV inverter will disconnect from the grid to ensure safety. However, if there is a slight disturbance in the frequency or voltage, the PV inverter will adjust its output active or reactive power to alleviate grid management. So, advance monitor and control technologies are needed for these PV functions [5-10].

For the PV inverters, high efficiency power electronics system and advanced functions capability are two essential future research and development targets. These two are also linked together, one improvement in one aspect will influence another aspect’s performance. Besides, the PV cells new improvement and power grid new requirement will also influence the overall PV inverter design and function definition.

My research work is supported by DOE Sunshot Project: *Field Verification of High-Penetration Levels of PV into the Distribution Grid with Advanced Power Conditioning Systems*. The main objective of this project is to verify and demonstrate existing and new solar power conditioning systems in the distribution grid while emphasizing current technological issues. Improvements are focused on high efficiency power electronics technologies, cost effectiveness power conversion system, and power system interactions functions [1].
1.2 State-of-the-art PV inverters

As shown in Figure 1.1, from the power level and application point view, solar conversion system can be divided into microinverter system, string inverter system, and central inverter system [14-21].

<table>
<thead>
<tr>
<th>Microinverter</th>
<th>String inverter</th>
<th>Central inverter</th>
</tr>
</thead>
<tbody>
<tr>
<td>Power: &lt;1 kW</td>
<td>Power: &lt;30 kW</td>
<td>Power: &gt;30 kW</td>
</tr>
<tr>
<td>Residential</td>
<td>Residential/Commercial</td>
<td>Commercial</td>
</tr>
<tr>
<td>Typically connected to one PV panel</td>
<td>Connected to one or few string of PV panel</td>
<td>Connected to multiple parallel PV strings</td>
</tr>
<tr>
<td>Panel level MPPT</td>
<td>String level MPPT</td>
<td>PV array level MPPT</td>
</tr>
<tr>
<td>CEC efficiency: around 96.5%</td>
<td>CEC efficiency: around 98%</td>
<td>CEC efficiency: around 98%</td>
</tr>
<tr>
<td>Cost/Watt: around 0.60$/W</td>
<td>Cost/Watt: around 0.33$/W</td>
<td>Cost/Watt: 0.22$/W</td>
</tr>
<tr>
<td>Don’t have reactive power capability</td>
<td>Don’t have reactive power capability</td>
<td>Have reactive power capability</td>
</tr>
</tbody>
</table>

![ABB Aurora MICRO-0.3](image1.png) ![SMA Sunny Boy 8000TLUS](image2.png) ![SMA Sunny Central 500CP](image3.png)

Figure 1.1 Microinverter, string inverter, and central inverter.

1.2.1 Microinverter

The power level of microinverter is usually less than 1 kW, which means it is only designed for one PV panel, so the Maximum power point tracking (MPPT) can be executed on panel level [14-18]. The main purpose of microinverter is for residential application. The overall system efficiency is around 96.5%, and all the commercial products on the market don’t have reactive power capability [110-114].
1.2.2 String inverter

The power level of string inverter is usually between 1 kW and 30 kW, and connected to one or few string of PV panels, so the MPPT can be executed on string level [18-21]. The main purpose of string inverter is for both the residential and commercial application. The overall system efficiency is around 97%, some commercial products can achieve around 98% high efficiency. Most commercial string inverter products don’t support reactive power generation [116-121].

1.2.3 Central inverter

The power level of central inverter is usually more than 30 kW, some can be several MW. One central inverter is connected a PV panel array, so the MPPT can be only executed on PV array level [18-21]. The central inverter is specially designed for PV plant. The overall system efficiency is around 97.5%, and all the central inverters are required to have reactive power generation capability [122].

1.3 State-of-the-art PV system structures

From the solar power conditioning system structure point view, the PV inverter system can be divided into five different structure.

1.3.1 Two-stage system with high frequency transformer and pseudo DC link

The two-stage PV system with high frequency transformer and pseudo DC link is show in Figure 1.2. The principle of this system is that: first dc to ac stage will generate a rectified sinusoidal waveform (pseudo DC link), an unfolding
inverter will operate at line frequency to convert the rectified sinusoidal waveform into the sine waveform synchronized with grid voltage. This structure is suitable for a PV system with isolation requirement, but without reactive power generation requirement. Quite a few microinverters use this system structure [18-20].

Figure 1.2 Two-stage system with high frequency transformer and pseudo DC link.

1.3.2 Two-stage system with high frequency transformer and DC link bus voltage

Two-stage system with high frequency transformer and DC link bus voltage is shown in Figure 1.3. Compared with Two-stage system with high frequency transformer and pseudo DC link, this system has a constant dc voltage bus, and the secondary stage is a high frequency switching inverter. This structure is suitable for a PV system with both isolation requirement and reactive power generation requirement. Compare with Two-stage system with high frequency transformer and pseudo DC link, this structure can just use the secondary inverter stage to deal with reactive power generation, and the first stage can be optimized design at high efficiency, so the overall efficiency and cost can be compatible [18-21]. This structure is adopted by both the commercial microinverter and string inverters.
1.3.3 **Two-stage system with non-isolated DC-DC and DC link bus voltage**

Two-stage system with high boost ratio non-isolated DC-DC and DC link bus voltage is shown in Figure 1.4. Compared with two-stage system with high frequency transformer and DC link bus voltage, the high frequency transformer can be changed into coupled inductor, with this change, the boost ratio of first stage and efficiency can be improved. This structure is suitable for a PV system without isolation requirement, but with reactive power generation requirement, and is adopt by microinverter design [18-21].

1.3.4 **Single-stage system with line frequency transformer**

One-stage system with line frequency transformer is shown in Figure 1.5. This PV system only have one stage power conversion, and isolated transformer is also line frequency. So the overall efficiency can be higher than above three different structures. The line frequency transformer turns ratio also provide the flexibility for system design. This structure is suitable for a
PV system with both isolation requirement and reactive power generation requirement. One drawback that constrain its application is the size of the line frequency transformer, which let this this structure is not popular in the microinverter application. Almost all the central inverter use this structure due to the high efficiency, isolation capability, and flexible design with transformer turns ration. This structure is also the first choice for the early-age string inverters, but it is almost replaced by the transformerless inverter under recently standard/code requirements [18-21].

1.3.5 Single-stage system without isolation transformer

The one-stage PV system without isolation transformer is shown in Figure 1.6. This inverter system is also named as transformerless inverter system. Due to no transformer exist and one stage power conversion, this inverter system has highest power conversion efficiency and also highest power density. The central inverter has the isolation requirement, but the new standard allow the microinverter and string to connect to the grid without isolation, so commercial microinverter and string inverter product use this transformerless inverter topologies [18-21].
1.4 Objectives of the research project

Transformerless inverter system allow the PV system can connect to grid without isolation transformer. But high efficiency motivation and new standard requirement bring new challenges to the inverter design, which is main focused on the power electronics circuit selection with different type power devices, and different pulse width modulation (PWM) technologies for different power electronics circuit, and new function capability, such as reactive power generation capability [22-31].

The research work in this project is to address these challenges that can lead to the next generation high performance transformerless inverter. The objectives of this research project can be summarized as follows:

- **High efficiency topology and circuit design**

  High efficiency is preferred for maxim solar energy extraction, high reliable/low cost/low volume inverter design, and fast custom investment return. The transformerless inverter topology, is adopted in the microinverter and string inverter, has the highest efficiency. State-of-the-art transformerless inverter can reached around 97% efficiency. With latest Silicon carbide (SiC)
devices, the efficiency have the potential to be over 98%, but suffer from higher cost. Some special transformerless inverter topology can achieve more than 98% efficiency with cost-effective super-junction metal–oxide–semiconductor field-effect transistors (MOSFETs), but reactive power generation capability is suffered. So high efficiency transformerless inverter is a challenge for cost and future standard consideration [32-60].

- **Common mode voltage/leakage current**

  Transformerless inverters don’t have isolation, but the standards has special requirement for the ground loop leakage current. The ground loop leakage current not only related to the common mode (CM) and differential mode (DM) noise, but also related to the transformerless inverter circuit design and PWM method. The detail analysis and mathematic expression of the ground loop leakage current is one challenge for the transformerless inverter design [62-78].

- **Reactive power capability with MOSFET**

  For traditional insulated-gate bipolar transistors (IGBTs) based PV inverters, the reactive power generation capability is easy to realize. Recent transformerless inverter success in adopt Super-junction MOSFET to have higher switching frequency and higher efficiency. SiC or gallium nitride transistors can replace IGBTs or MOSFETs for better performance, but high cost power devices will be inconsistent with low cost PV system requirement. But all the commercial transformerless inverter product that using MOSFET
can’t do reactive power generation. So MOSFETs based high efficiency transformerless inverter with reactive power capability is one challenge for the transformerless inverter product [79-95].

- **Inverter function for grid connection**

  Grid connection function of PV inverter is also very important, and these advanced functions can be the heart for future PV plant. In order to stably convert the solar power into the power grid, the system modeling and control (current loop, voltage loop) is an essential part. If the power grid voltage or frequency has some disturbance, the PV inverter should have fast enough detection system to do proper response, so the system detection and control is also an essential part [61], [96-109].

### 1.5 Outline of the dissertation

The present chapter provides a general overview regarding the topic of PV inverter and discusses the research motivation behind this work. The main objectives and major contributions of this dissertation is given. A brief explanation of the research problems discussed in each chapter is given as follows:

- **Chapter 2: High Efficiency transformerless inverter with advanced neutral point clamping technology.** This chapter begins with a brief history of transformerless inverter for PV application. The three-level neutral point clamped (NPC) inverter topology is reviewed for high power PV system application. State-of-the-art transformerless inverter topologies are
reviewed, a new technology is summarized, which named neutral point virtually clamped (V-NPC) inverter technology. Based on this summarized V-NPC technology, a family of high efficiency transformerless inverters are proposed and verified. For the high dc input transformerless inverter application, an improved V-NPC technology is also proposed, with the improved V-NPC technology, a family single-phase inverter circuits is proposed and verified.

- **Chapter 3: MOSFET based transformerless inverter with high magnetic utilization.** Through a brief overview of MOSFET based high efficiency transformerless inverters, a novel MOSFET based phase leg is proposed in this chapter. Proposed MOSFET based phase leg not only can avoid MOSFET body diode reverse recovery issues, can achieve high magnetic utilization, but also can be used in almost all the transformerless inverter topologies to replace IGBTs to have higher efficiency. With proposed novel MOSFET based phase-leg method, a high efficiency MOSFET based transformerless inverter is presented, circuit analysis and hardware prototype will demonstrate the proposed inverter topology. The general application of this proposed MOSFET based phase-leg is also demonstrated in different inverter topologies.

- **Chapter 4: Reactive power generation on MOSFET based transformerless inverter.** This chapter will introduce the reactive power generation of PV inverter. These upcoming standards will require all the PV inverters to
have reactive power capability. The state-of-the-art MOSFET based transformerless inverter don’t have reactive power capability. The high efficiency MOSFET based transformerless inverter proposed in chapter 3 has the capability for reactive power generation. This chapter will mainly focus on how to improve the inverter circuit, how to generate proper PWM for reactive power generation, and how to design the system component to minimize the low common mode voltage.

- **Chapter 5: Grid Connection Analysis and Design.** This chapter will focus on the modeling, control, and system design for grid-connection functions. The current loop and voltage loop is modeled for the grid connection system. The dynamic reactive power generation, the grid information detection with improved method is also present in this chapter for fast dynamic response.

- **Chapter 6: Conclusions and Future Work.** This chapter summarizes the outcomes of the work presented in this research project and concludes the thesis. Based on the experimental results, recommendations for future work are also presented.
2.1 Introduction

With worldwide growing demand for electric energy, there has been a great interest in exploring photovoltaic (PV) sources. As the energy conversion key component, PV inverter system implementation method is always being improved for the efficiency concern and standard requirement. Since the 1984, the Section 690.41 of National Electrical Code (NEC) required a grounded conductor for PV inverter where the dc voltage is over 50V [22],[23]. With both the dc source and the utility grid grounded, the PV inverter system needs an isolation transformer, as shown in Figure 2.1, to allow dc to ac conversion.

![Figure 2.1 PV inverter system with transformer.](image)

After the section 690.35 was added into the NEC 2005[24], [25], and the section 690.35(D) was added to the NEC 2008[26], The PV system in North America is allowed to operate with ungrounded PV source. As shown in Figure 2.2, with the PV source ungrounded, the transformerless PV inverter can be adopted, which can eliminate the bulky isolation transformer to improve the system efficiency and reduce the inverter size, volume, and the cost.
In the transformerless PV inverter system, even if the dc voltage source is floating, the PV metal frame is still grounded. The parasitic capacitance between the PV array cells and the metal frame will introduce an equivalent parasitic capacitance in the ground loop, which is shown in Figure 2.3, and the parasitic capacitance is referred as $C_{G-PV}$. If the high frequency common mode voltage (CM) voltage and differential mode (DM) voltage are not well controlled, there will be a high frequency ground loop voltage on this parasitic capacitor, and a high-frequency leakage current will be generated [62]-[78]. This leakage current can cause distortion and harmonic, high losses, safety issue, fault protection and electron magnetic interference. The requirements for limiting ground loop leakage current and fault current can be referred to VDE0126-1-1, and UL 1741 [27], [28].
As discussed above, transformerless inverter can eliminated the isolation transformer for higher efficiency, smaller volume and lower cost, but special inverter topologies and PWM modulation methods are needed for low CM voltage on parasitic capacitor [65]-[68]. This paper will begin with a brief overview of the state-of-the-art single-phase transformerless inverter topologies in chapter 2.2.3. The V-NPC technology will be summarized in the chapter 2.3. A family of single-phase transformerless inverters based on V-NPC technology will be proposed in the chapter 2.4. The PWM scheme and operating mode of proposed transformerless inverter will also be detailed in the chapter 2.4.2. Power loss analysis in the power stage and efficiency calculation will be presented in the chapter 2.4.3. Experimental results will be shown in the chapter 2.4.4 to verify proposed inverters. A family of inverter circuit with improved V-NPC technology for high input dc voltage application will be proposed in 2.5, experimental results will also be shown to demonstrate the improved V-NPC method.

2.2 State-of-the-art transformerless inverters

In recent years, there is a considerable amount of innovations on transformerless PV inverters [32-39], which eliminate traditional line frequency transformers to reach lower cost and higher efficiency, and maintain lower leakage current at the same time. The earliest and the most common one is neutral point clamp (NPC) inverter [46],[47]. Compared with two level phase leg, the three-level inverter has lower voltage stress devices, lower inductor
voltage stress. The advantage of three level not only can boost switching frequency and efficiency to shrink the passive component and heatsink, but also can improve control system bandwidth, EMI and audible noise.

As shown in Figure 2.4 Neutral point clamp (NPC) inverter [46], the traditional diode clamped NPC inverter, which needs high DC voltage, is widely used in medium solar power inverter (10kW to 20kW) [121]. The neutral point clamped inverter or T-type NPC inverter topology is shown in Figure 2.5. Compared with NPC inverter, the Conergy NPC inverter uses a pair of auxiliary freewheeling switches (S₃ and S₄) to achieve neutral point clamping. The voltage rating of S₁ and S₂ is the full dc bus voltage, but the device voltage stress during switching period is half of dc bus voltage, and the conduction loss can be reduced compared with NPC topology.

For the medium solar power inverter, 1200V IGBT is the first the choice for commercial product. As reported in [79], SiC MOSFET or SiC JFET has better performance but higher cost. Commercial product Sunny Tripower 20000TL of SMA reported they achieved 98.5% efficiency by using Conergy NPC inverter with dc bus voltage between 450 V and 800 V.

![Figure 2.4 Neutral point clamp (NPC) inverter](image)

Figure 2.4 Neutral point clamp (NPC) inverter
Another improved NPC inverter is shown in Figure 2.6. This improved NPC topology uses two MOSFETs and two IGBTs, the MOSFETs will switch at high frequency and IGBT will switch at line frequency for active power generation. The combination of MOSFET and IGBT can achieve high efficiency by using MOSFET's high switching speed and IGBT's low conduction loss. Besides, the IGBTs don't have anti-parallel diode, so the MOSFETs will have none body diode reverse recovery issue. Well packaged module of this bridge topology are provided by several Semiconductor Company.

For the lower power level solar inverter (below 10kW, DC bus is around 300V to 600Vdc), most of the manufacture try to use innovative transformerless inverter topology to boost the efficiency.
The simplest PV transformerless inverter topology is the H-bridge inverter, as shown in Figure 2.7, which utilizes the insulated-gate-bipolar-transistors (IGBTs) as the power device. The advantages of this inverter topology are its simple structure and capability of producing reactive power. The main drawback for this inverter design is it requires the use of bipolar PWM modulation to avoid the common mode (CM) voltage [41]. As a result, the efficiency suffers due to high switching loss on IGBTs, high current ripple induced core and copper losses on the output filter inductor. The ABB’s string inverter PVI-5000-OUTD-US adopts this IGBT based H-bridge topology. Its maximum efficiency is 97.1%, and the California Energy Commission (CEC) weighted efficiency is 96.5% [116]. The CEC efficiency suffers because IGBT has a fixed voltage drop that significantly reduces the light-load efficiency and also the low switching speed.

The metal oxide semiconductor field effect transistor (MOSFET) voltage drop is a resistive and is preferred for maintaining high efficiency under light-load conditions and also for fast switching speed. However, high-voltage MOSFETs suffers from the slow reverse recovery and snappy body diode, which not only produces high dv/dt, di/dt, and high power loss, but also creates phase-leg shoot through risk due to reverse conducting current [84]-[89]. Therefore, high-voltage MOSFETs are not suitable for this H-bridge topology.
The Highly Efficient and Reliable Concept (HERIC) inverter topology [55], shown in the Figure 2.8 may adopt IGBT or MOSFET as the main switch. This novel inverter circuit utilizes a pair of ac switches (S₅/D₅ and S₆/D₆) to decouple the PV panel from the grid during current freewheeling period to minimized the common mode voltage [49], [58]. Its associated unipolar modulation method allows the reduction the switching loss and the core loss of the output filer. Compared with the bipolar modulation, the power device switching loss, core loss and inductor voltage stress can be all reduced. When the HERIC inverter is working under unity power factor condition, antiparallel diodes of S₁ to S₄ will not conduct the current, so power MOSFETs can be used. In the MOSFET based inverter that is similar to HERIC inverter [48] and [49], 99% efficiency is reported by using high-voltage MOSFETs. However, when the HERIC inverter is working under reactive power generation, the antiparallel diodes of main switches will conduct the current, and it is difficult to use MOSFET for reactive power generation due to the body diode reverse recovery problem. A commercial product, NT 5000 solar inverter from Sunways, uses
the HERIC inverter topology but adopting IGBTs as the main switch to achieve reactive power generation, the power factor (PF) range is 0.9 over-excited to 0.9 under-excited. Its maximum efficiency and European Common (EC) efficiency are reported at 97.8% and 97.5%, respectively [117]. As compared with 4-IGBTs based H-bridge inverter with bipolar modulation, the HERIC inverter needs two more active switches and two more diodes, but the system efficiency is improved, and the filter inductor and heat sink sizes are reduced.

![Diagram of the HERIC inverter with paralleled auxiliary freewheeling switches]

Figure 2.8 The HERIC inverter with paralleled auxiliary freewheeling switches

The principle of the unipolar modulation in [34] is that: in the positive half grid cycle, the S₁ and S₄ will be switched simultaneously in high frequency, and the S₅ is turned on in entire positive grid cycle; In the negative half cycle, the S₂ and S₃ will be switched simultaneously in high frequency, and the S₆ is turned on in entire positive grid cycle. The auxiliary freewheeling switches can be two sets of unidirectional switches connected in anti-paralleled configuration, as shown in Figure 2.8, or two devices connected in back-to-back configuration, as shown in Figure 2.9 [58]. The diode in the back-to-back series auxiliary freewheeling switch configuration needs to be fast recovery diode or schottky diode to reduce the diode reverse recovery loss.
Another high-efficiency commercial PV inverter product is the Sunny Boy 6000TL-US to 11000TL-US series inverters from the SMA [118]. This series Sunny Boy inverters use the H5(TM) transformerless inverter topology [57],[59], which is shown in the Figure 2.10. By using the switches of S1 and S3 to decouple the PV panel from grid during current freewheeling, the H5(TM) inverter topology can also use unipolar PWM. This inverter topology has three devices in series in the current conduction loop, so the conduction loss of power stage is slight higher than the HERIC inverter. The Sunny Boy 9000TL-US uses the MOSFETs for the high switching frequency devices S2, S4, and S5, and IGBTs for low switching frequency (line frequency) devices S1 and S3, all the power devices are packaged in one power module. This 9-kW inverter reports the maximum and CEC efficiencies at 98.7% and 98.0%, respectively [118]. This MOSFET based inverter can achieve relatively high efficiency, but it can only operate under unity power factor condition. On the other hand, a similar power rated product Sunny Mini Central 9000TL inverter also uses the H5 topology, but adopting IGBTs for all power switches to realize 0.8 over-excited to 0.8 under-excited reactive power generation. Its reported maximum efficiency,
However, is reduced from 98.7% to 97.7%, which implies the power loss is increased from 1.3% to 2.3%. As compared to Sunny Boy 9000TL-US, the efficiency is reduced by 1%, but from power loss point of view, the IGBT based inverter increases the power loss by 77% [128].

![H5 inverter topology](image)

Figure 2.10 The H5™ inverter topology

One patent-free transformerless inverter is the H6 inverter [40], which is shown in Figure 2.11. Compared with the HERIC inverter, the H6 inverter also use a pair of auxiliary freewheeling switches (S5/D5, S6/D6) to separate the grid from PV dc source. Compared with the H5 inverter, the auxiliary freewheeling switches of the H6 inverter is also plugged into the H-bridge. The advantage of the H6 inverter over the H5 inverter is that it can adopt CoolMOS to replace the IGBTs for auxiliary freewheeling switches (S5 and S6), which can reduce the low load conduction loss with MOSFET. This patent-free topology achieves 98.1% CEC efficiency under 300 W condition, but needs one more active switch compared with H5 topology and also has 3 devices in the conduction loop.
As shown in Figure 2.12, reference [62] splits $S_5$ of H5 topology into $S_5$ and $S_6$ in series and operates them in high frequency switching, $S_1$~$S_4$ in line grid line frequency switching. With this structure, the system configuration is more symmetrical, so this inverter can be named as symmetrical H6 inverter topology in this dissertation. Two pair of auxiliary freewheeling switches ($S_1$/$S_2$, $S_4$/$S_3$) are used to separate the grid from PV dc source during the current freewheeling. By switching $S_1$~$S_4$ in high frequency, paper [62] introduces a double frequency modulation method, which can reduce the output filter at the cost of increasing switching loss. Drawbacks of this inverter are more switching loss and more conduction loss (4 devices in conduction loop).
Another high efficiency transformerless inverter patented by SMA is shown in the Figure 2.13, which consists of one half H-bridge phase-leg and one neutral point clamping phase-leg [60]. The clamping diode is connected to the one of the inverter output terminals. The middle four devices in the neutral point clamping bridge leg are severed as the auxiliary freewheeling switches (S₅/D₅ and S₆/D₆).

![Figure 2.13 The hybrid phase leg inverter topology](image)

**2.3 Neutral point virtually clamped (V-NPC) technology with auxiliary freewheeling switches**

With a brief overview of the state-of-the-art high dc input voltage, medium power level transformerless inverter in the chapter 2.2, all the inverter topologies use the neutral point clamping method, which can let output filter been clamped to dc bus neutral point through a pair of auxiliary freewheeling switches during the current freewheeling.

As shown in Figure 2.14, for the NPC inverter, the output filter will be clamped to dc bus neutral point through auxiliary freewheeling switches (S₂/S₃, D₅/D₆) during the current freewheeling period.
As shown in Figure 2.14, for the T-type NPC inverter, the output filter will be clamped to dc bus neutral point through auxiliary freewheeling switches (S3/S4) during the current freewheeling period. With this neutral point clamping, the ground loop voltage and common mode voltage for NPC and T-type inverter will be a constant low frequency component.

With the brief overview of the state-of-the-art low dc input low power level transformerless inverter in the chapter 2.2 from Figure 2.8 to Figure 2.13, a common characteristic can be found that all theses transformerless inverters use a pair of auxiliary freewheeling switches to separate the PV panel from grid during the current freewheeling period.

As shown in Figure 2.16, the auxiliary freewheeling switches (S5/S6) of the HERIC inverter will separate the output filter from the dc bus during the
freewheeling, and the voltage level of the output filter will be equal to the neutral point of dc bus, so the output filter is virtually clamped to the dc bus neutral point.

As shown in Figure 2.17, the auxiliary freewheeling switches (S5/D5/S6/D6) of the H6 inverter will separate the output filter from the dc bus during the freewheeling, and the voltage level of the output filter will be equal to the neutral point of dc bus.

As shown in Figure 2.18, the auxiliary freewheeling switches (S5/S6) of the H5 inverter will separate the output filter from the dc bus during the
freewheeling, and the voltage level of the output filter will be equal to the neutral point of dc bus.

![Image of H5 inverter](image1)

**Figure 2.18 Current freewheeling path of H5 inverter**

As shown in Figure 2.19, the auxiliary freewheeling switches (S1/S2/S3/S4) of the symmetrical H6 inverter will spate the output filter from the dc bus during the freewheeling, and the voltage level of the output filter will be equal to the neutral point of dc bus.

![Image of H6 inverter](image2)

**Figure 2.19 Current freewheeling path of symmetrical H6 inverter**

As shown in Figure 2.20, the auxiliary freewheeling switches (S5/D5/S6/D6) of the hybrid phase leg inverter will spate the output filter from the dc bus during the freewheeling, and the voltage level of the output filter will be equal to the neutral point of dc bus.

![Image of hybrid inverter](image3)
In conclusion, all these transformerless inverter use a pair of auxiliary freewheeling switches to provide current freewheeling path. For the NPC or T-type inverters, the output filter will be clamped to the neutral point of dc bus. For these low voltage/low power level transformerless inverters, the voltage level of the output filter will be virtually clamped to the dc bus neutral point. With the virtually clamping method, the inverter system will have the similar common mode and ground loop voltage performance compared with the traditional NPC method. This new multilevel method will be named as neutral point virtually clamped method (V-NPC).

2.4 A family of high-efficiency transformerless inverter circuits with V-NPC Technology

With the brief overview of the state-of-the-art transformerless inverter in the chapter 2.3, a new multilevel technology V-NPC can be summarized. All of these new transformerless inverter use a pair of auxiliary freewheeling switches to separate the PV panel from grid during the current freewheeling period. The auxiliary freewheeling switches of the HERIC inverter is on the
grid side; auxiliary freewheeling switches of the H6 inverter is in the H-bridge phase-legs, and each leg has one active switch; H5 inverter combines two phase-leg top switches (S1 and S3) of the H6 inverter into one switch (S1); the hybrid phase leg inverter put all the auxiliary freewheeling switches in one of the phase-leg; the symmetrical H6 inverter use the middle H-bridge as the auxiliary freewheeling switches.

2.4.1 Proposed inverter topologies

Based on the above overview and analysis, a new family of transformerless single-phase inverters also based on V-NPC method are present in Figure 2.21. The basic idea of these proposed transformerless inverters is that half of the auxiliary freewheeling switches are put in the middle of one phase-leg, another half auxiliary freewheeling switches are put between the two phase legs. As shown in Figure 2.21(a), the H-bridge consists of the S1, S2, S5, and S6; the auxiliary freewheeling switches are the S5 and S6. In this case, the S6 is put between the phase-leg of S1 and S2, and the S5 is put between two phase-legs. A dual circuit for the inverter circuit in Figure 2.21(a) is presented in the Figure 2.21(b). Actually, more inverter circuit can be derived with different arrangement from Figure 2.21(a) and Figure 2.21(b). Figure 2.21(c) and Figure 2.21(d) present similar inverter circuits with paralleled auxiliary freewheeling switches structure (S5/D5 and S6/D6).
(a) Topology 1

(b) Topology 2

(c) Topology 3
2.4.2 PWM method and working principle

The PWM implementation circuit for proposed transformerless is presented in Figure 2.22. Figure 2.23 shows the PWM gating signals in the Figure 2.22. In the positive half grid cycle, voltage reference signal $V_{\text{ref}}$ is compared with the carrier signal $V_{\text{carrier}}$, and the output signal is used to drive the devices $S_1$ and $S_4$, which are switched simultaneously in high frequency; voltage reference signal $V_{\text{ref}}$ is compared with zero and outputs a high level signal to turn on $S_5$ in the entire positive grid cycle, which operates as a polarity selection in grid line frequency. In the negative half grid cycle, inverted voltage reference signal $V_{\text{ref-inv}}$ is compared with the carrier signal $V_{\text{carrier}}$, and the output signal is used to drive the devices $S_2$ and $S_3$, which are switched simultaneously in high frequency; the $S_6$ is turned on in the entire positive grid cycle.
The four different operation modes of the proposed inverter topology 1 in Figure 2.22(a) are shown in Figure 2.24. In the positive half grid cycle, voltage reference signal $V_{ref}$ is compared with the carrier signal $V_{carrier}$ to produce the gating driver signals for the devices $S_1$ and $S_4$, which are switched simultaneously in high frequency; voltage reference signal $V_{ref}$ is compared
with zero and outputs a high level signal to turn on S₅ in the entire positive grid cycle, which operates as a polarity selection in grid line frequency. When the S₁ and S₄ are turned on, as shown in Figure 2.24 (a), current will flow from dc side to ac grid side through S₁ and S₄; when S₁ and S₄ are turned off, as shown in Figure 2.24 (b), the free-wheeling current will flow through S₅ and S₆. In the negative half grid cycle, the inverse signal of the voltage reference signal V_{ref, inv} is compared with the carrier signal V_{carrier} to drive the devices S₂ and S₃, which are switched simultaneously in high frequency; the S₆ is turned on in the entire positive grid cycle. When the S₂ and S₃ are turned on, as shown in Figure 2.24(c), current will flow from dc side to ac grid side through S₂, S₃, and S₆; when S₂ and S₃ are turned off, as shown in Figure 2.24 (d), the free-wheeling current will flow through S₅ and S₆.
Figure 2.24 Operating modes of the proposed transformerless inverter Topology 1 in Figure 2.21(a): (a) Positive half-line cycle, S1 and S4 are on, (b) Positive half-line cycle, S1 and S4 are off, free-wheeling current goes through S5 and S6, (c) Negative half-line cycle, S3 and S2 are
on, (d) Negative half-line cycle, S₅ and S₆ are off, freewheeling current goes through S₅ and S₆.

The four different operation modes of the proposed inverter topology 3 in Figure 2.21(c) is shown in Figure 2.25. The operation of inverter topology 3 is very similar to that of the inverter topology 1 in Figure 2.25. In the positive half line cycle, the S₅ is always on, when S₁ and S₄ are turned off, the free-wheeling current will go through S₅ and D₅, which is shown in the Figure 2.25 (a) and Figure 2.25 (b). In the negative half line cycle, the S₆ is always on, when S₂ and S₃ are turned off, the free-wheeling current will go through S₆ and D₆, which is shown in the Figure 2.25 (c) and Figure 2.25 (d).
Figure 2.25  Operating modes of the inverter 3 in Figure 2.21(c): (a) Positive half-line cycle, 
$S_1$ and $S_4$ are on, (b) Positive half-line cycle, $S_1$ and $S_4$ are off, free-wheeling current goes 
through $S_5$ and $D_5$, (c) Negative half-line cycle, $S_3$ and $S_2$ are on, (d) Negative half-line cycle, 
$S_3$ and $S_2$ are off, freewheeling current goes through $D_6$ and $S_6$.

Simulation results of the operating modes of the proposed inverter topology 
1 is shown in Figure 2.25 (I). As shown in Figure 2.25 (I)-(a), the gating signals 
and ac voltage waveforms match with the unipolar modulation method shown 
in Figure 2.25 and Figure 2.25.
Detailed gating signals, voltage waveforms, and current waveforms in two switch cycles for positive half line cycle and negative half line cycle are shown in Figure 2.26(I)-(b) and Figure 2.26(I)-(c) respectively. In the positive half line cycle, as shown in Figure 2.26 (I)-(b), S₁ and S₄ are both switching at high frequency, S₅ are always turned on, other devices are turned off, when S₁ and S₄ are turned on, they will conduct the output filter inductor current i_{LF1}; when S₁ and S₄ are turned off, current will free-wheeling through the S₅ and S₆. In the negative half line cycle, as shown in Figure 2.26 (I)-(c), S₂ and S₃ are both switching at high frequency, S₆ are always turned on, and other devices are turned off. When S₂ and S₃ are turned on, the S₂, S₃ and S₆ will conduct the output filter inductor current i_{LF1}; when S₂ and S₃ are turned off, current will free-wheeling through the S₅ and S₆.

For the proposed inverter topology 3, simulation results are shown in Figure 2.26 (II). The PWM gating signals are as same as results in Figure 2.26 (I). The difference is the current waveforms in the auxiliary freewheeling switches (S₅ and S₆). As shown in Figure 2.26 (II)-(b), in the positive half line cycle, when S₁ and S₄ are turned on, they will conduct the output filter inductor current i_{LF1}; when S₁ and S₄ are turned off, current will free-wheeling through the S₅. In the negative half line cycle, as shown in Figure 2.26 (II)-(c), when S₂ and S₃ are turned on, the S₂, S₃ and S₆ will conduct the output filter inductor current i_{LF1}; when S₂ and S₃ are turned off, current will free-wheeling through the S₆.
Figure 2.26  Simulation results of: (I) Topology 1 in Figure 2.21 (a); (II) Topology 3 in Figure 2.21 (c)
2.4.3 Efficiency calculation and loss analysis

The efficiency calculation and loss analysis are carried out for the proposed transformerless inverter topology 1 in Figure 2.21 (a). All the power devices in the inverter are 650V SiC MOSFET with the part number SCT2120AFC [129]. The inverter is running at 30 kHz switching frequency, the input dc voltage is 380V, the ac output voltage is 240 V, and the nominal output power is 250W. The losses in the inverter can be divided into the power devices loss (conduction loss, switching loss), and output inductor loss (winding loss and magnetic core loss).

The voltage drop of MOSFETs can be simplified as a channel resistor, the voltage drop of device body diodes can be simplified as a voltage source series with a channel resistor, which are shown in (2.1) and (2.2) respectively.

\[
v_{ds} = i \cdot R_{ds} \quad \text{(2.1)}
\]

\[
v_{ak} = V_f + i \cdot R_{ak} \quad \text{(2.2)}
\]

Assuming the output current is in-phase with the duty cycle, which refers to pure active generation condition, the output current can be expressed as:

\[
i(t) = I_m \cdot \sin(\omega t) \quad \text{(2.3)}
\]

For the inverter topology 1 in Figure 2.21 (a), all the high frequency MOSFETs (S1 and S4) power devices work in the positive half of the line cycle. For the positive half cycle, the duty cycle of S1, S4 can be expressed as (2.4); the duty cycle of the S5 can be expressed as (2.5).
\[ d_{s, s_1} = M \cdot \sin(\omega t) \quad (2.4) \]
\[ d_{s_5} = 1 \cdot M \cdot \sin(\omega t) \quad (2.5) \]

So the conduction loss of \( S_1 \) or \( S_4 \) is:

\[
P_{\text{Conduction}_{s_1/S_4}} = \frac{1}{2\pi} \int_0^\pi i(t) \cdot v_{ds}(t) \cdot d_{s, s_1} \cdot d(\omega t) = I_m^2 R_{ds} \frac{2M}{3\pi} \quad (2.6)
\]

The channel of the \( S_5 \) and the body diode of the \( S_6 \) work in the positive half of the line cycle. They share the same duty cycle, so the conduction loss on the channel resistor of \( S_5 \) and the body diode of \( S_6 \) is:

\[
P_{\text{Conduction}_{s_5}} = \frac{1}{2\pi} \int_0^\pi i(t) \cdot v_{ds}(t) \cdot d_{s_5} \cdot d(\omega t) = I_m^2 R_{ds} \left( \frac{1}{4} - \frac{2M}{3\pi} \right) \quad (2.7)
\]

\[
P_{\text{Conduction}_{s_6, \text{Diode}}} = \frac{1}{2\pi} \int_0^\pi i(t) \cdot v_{ak}(t) \cdot d_{s_6} \cdot d(\omega t) = I_m V_f \left( \frac{1}{\pi} - \frac{M}{4} \right) + I_m^2 R_{ak} \left( \frac{1}{4} - \frac{2M}{3\pi} \right) \quad (2.8)
\]

Power losses of the \( S_2, S_3 \) in the negative half cycle are as same the switch \( S_1 \) and \( S_4 \) due to the symmetric operation modes. So, the conduction loss of the \( S_2 \) or \( S_3 \) can be expressed as:

\[
P_{\text{Conduction}_{s_2/S_3}} = P_{\text{Conduction}_{s_1/S_4}} = I_m^2 R_{ds} \frac{2M}{3\pi} \quad (2.9)
\]

The current in the channel of \( S_6 \) is continuous for the negative half cycle, so the channel conduction loss can be expressed as:

\[
P_{\text{Conduction}_{s_6}} = I_m^2 R_{ds} \frac{2M}{3\pi} + I_m^2 R_{ds} \left( \frac{1}{4} - \frac{2M}{3\pi} \right) \quad (2.10)
\]

\[ = I_m^2 R_{ds} \frac{1}{4} \]
The body diode conduction loss of the S_5 in the negative half cycle is:

\[ P_{\text{Conduction \_ S_5 \_ Diode}} = I_m \cdot V_f \cdot \left( \frac{1}{\pi} - \frac{M}{4} \right) + I_m^2 \cdot R_{ak} \cdot \left( \frac{1}{3\pi} - \frac{2M}{3\pi} \right) \quad (2.11) \]

So, the total power devices conduction loss in the proposed transformerless inverter in Fig. 12(a) is:

\[ P_{\text{Conduction \_ Proposed}} = 4P_{\text{Conduct \_ S1 \_ S2 \_ S3 \_ S4}} + 2P_{\text{Conduct \_ S5 \_ Diode}} + P_{\text{Conduct \_ S6}} + P_{\text{Conduct \_ S6}} \]

\[ = 4I_m^2 \cdot R_{ds} \cdot \frac{2M}{3\pi} + 2I_m \cdot V_f \cdot \left( \frac{1}{\pi} - \frac{M}{4} \right) + \]

\[ 2I_m^2 \cdot R_{ak} \cdot \left( \frac{1}{4} - \frac{2M}{3\pi} \right) + I_m^2 \cdot R_{ds} \cdot \frac{1}{4} + \]

\[ (2.12) \]

In the proposed inverter in Figure 2.21 (a), S_5 and S_6 are switching at line frequency, so the switching loss from them can be ignored. Switches S_1 to S_4 are switching at high frequency, and the switching loss from these devices can be divided into: (1) the voltage and current overlap losses during turn on; (2) the turn on loss from diode reverse recovery; (3) the device output capacitor energy discharge losses; (4) the voltage and current overlap losses during turn off [43].

During the switch turning on, there are two stages: the first stage begin with the device gate-source voltage (V_{GS}) equals to the threshold voltage (V_{th}), and end with V_{GS} equals to the plateau voltage (V_{pla}). The time (T_{r1}) of the first stage can be calculated through the gate driver voltage V_{DD}, gate driver resistor R_g, and the gate source charge (Q_g) curve with gate voltage [80]. The time (T_{r1}) can be calculated through (2.13):
\[
\int_{t_{on}}^{t_{on}+T_{r1}} \frac{V_{DD} - V_{GS}(t)}{R_g} dt \approx Q_g \left|_{V_{GS}=V_{pl}} - Q_g \right|_{V_{GS}=V_{th}}
\]

(2.13)

During the first stage, the drain-source voltage almost keep constant, the drain current rise from zero to peak value \((I_{ds})\) [80], so current and voltage overlap loss can be estimated as:

\[
P_{SW_{on-1}} = f_{sw} \cdot \int_{t_{on}}^{t_{on}+T_{r1}} i_d(t) \cdot v_{ds}(t) \cdot dt \approx f_{sw} \cdot \frac{I_{ds}}{2} \cdot V_{ds} \cdot T_{r1}
\]

(2.14)

The secondary stage happens during the \(V_{GS}\) equals to the plateau voltage \((V_{pl})\), and the drain current keep as constant, the drain-source voltage drop to zero in this period. The time \((T_{r2})\) can be calculated through (2.15), and the current and voltage overlap loss can be estimated as (2.16).

\[
\int_{t_{on}+T_{r1}}^{t_{on}+T_{r1}+T_{r2}} \frac{V_{DD} - V_{GS}(t)}{R_g} dt \approx \Delta Q_g \left|_{V_{GS}=V_{pl}}
\]

(2.15)

\[
P_{SW_{on-2}} = f_{sw} \cdot \int_{t_{on}+T_{r1}}^{t_{on}+T_{r1}+T_{r2}} i_d(t) \cdot v_{ds}(t) \cdot dt \approx f_{sw} \cdot \frac{I_{ds}}{2} \cdot V_{ds} \cdot T_{r2}
\]

(2.16)

During the switch turning off, there are also two stages [80]: the first stage begin with the device gate-source voltage \((V_{GS})\) drop to the threshold voltage \((V_{th})\), and \(V_{GS}\) will stay at \(V_{th}\) for a time of \(T_n\). In this stage, the time \((T_n)\) can be calculated through (2.15), the only difference is the gate driver voltage is changed. During this stage, the drain current will keep constant, the drain-source voltage will rise up from zero to maximum, so the current and voltage overlap loss can be estimated as (2.17).

\[
P_{SW_{off-1}} = f_{sw} \cdot \int_{t_{off}}^{t_{off}+T_{r1}} i_d(t) \cdot v_{ds}(t) \cdot dt \approx f_{sw} \cdot \frac{I_{ds}}{2} \cdot V_{ds} \cdot T_{r1}
\]

(2.17)
The secondary stage happens during the device gate-source voltage \( V_{GS} \) drops from the plateau voltage \( V_{pla} \) to the threshold voltage \( V_{th} \). The time \( T_{f2} \) be calculated through (2.15) with related turn off gate driver voltage. During this stage, the drain-source voltage will keep constant, the drain current will drop from maximum to zero, so the current and voltage overlap loss can be estimated as (2.18).

\[
P_{SW\_off-2} = f_{sw} \cdot \int_{t_{off}+T_{r1}+T_{r2}}^{t_{off}+T_{r1}} i_d(t) \cdot V_{ds}(t) \cdot dt \approx f_{sw} \cdot V_{ds} \cdot \frac{I_{ds}}{2} \cdot T_{r2} \quad (2.18)
\]

During the switch turning on, there is a diode reverse recovery [80], which will result the loss of:

\[
P_{rr} = f_{sw} \cdot V_{dc} \cdot Q_{rr} \quad (2.19)
\]

Besides, the device output capacitor energy will be discharged in the device during the device turning on [80], and this output capacitor energy discharge losses can be calculated as:

\[
P_{Coss} = f_{sw} \cdot E_{Coss} \quad (2.20)
\]

So the total switching loss can be expressed as:

\[
P_{SW\_Loss} = f_{sw} \cdot V_{ds} \cdot \frac{I_{ds}}{2} \cdot (T_{r1} + T_{r2} + T_{r1} + T_{r2}) + f_{sw} \cdot V_{dc} \cdot Q_{rr} + f_{sw} \cdot E_{Coss} \quad (2.21)
\]

The conduction loss in the inductor can be divided into the line frequency current conduction loss which is related to the dc resistance \( R_{L,DC} \), and the switching frequency current ripple conduction loss which is related to the switching frequency ac resistance \( R_{L,AC} \). The total conduction losses are:
The core loss can be calculated through core cross section volume $V$, and the core loss density $P_L$:

$$P_{\text{core}} = P_L \cdot V$$

(2.23)

The core loss density is a function of the ac flux swing and frequency. It can be approximated from the core loss charts or the curve fitted loss equation from magnetic datasheet.

$$P_L = a\Delta B^b f^c$$

(2.24)

For the PV inverters, the California Energy Commission (CEC) provides an efficiency calculation method (referred as CEC efficiency) [48], [49], which is based on the weighted efficiency calculation at different output power levels (10%, 20%, 30%, 50%, 75%, and 100% of the full power level). In this paper, the efficiency of the proposed inverter power stage in Figure 2.23 (a) are all calculated according to the CEC calculation method for a micro-inverter with 250-W rating (Note: the efficiency calculation only take account the power state, the auxiliary circuit losses and control circuit losses are not included). The loss distribution of inductor conduction loss, inductor core loss, device conduction loss, and device switching loss under different power level is shown in Figure 2.23. The calculated total losses and efficiency for different power level are presented in the Figure 2.23.
2.4.4 Experimental Results

A 250 W micro-inverter with 380 V dc input and 240 V ac output has been designed and built to verify the performance. The photograph of the hardware prototype is shown in the Figure 2.23. The inverters are switching at 30 kHz. The output filter inductor is 4.7 mH with EPCOS N95 ferrite materials[123],[124], output filter capacitor is 0.47uF, and all the power devices are SCT2120AFC.
The PWM gating signals for the proposed transformerless inverter in Figure 2.23 (a) are shown in Figure 2.23. As shown in Figure 2.23 (a), in the positive half cycle, $S_1$ and $S_4$ are switched simultaneously in high frequency PWM and $S_5$ is always on. As shown in Figure 2.23 (b), in the negative half cycle $S_2$ and $S_3$ are switched simultaneously in high frequency PWM and $S_6$ is always on. The experimental results in Figure 2.23 match well with the PWM gating signals in Figure 2.23 and simulation results in Figure 2.23 (I).
Figure 2.30  PWM gate signals waveforms for proposed inverter

Figure 2.31  Output voltage/ current and ground loop voltage waveforms

Figure 2.32  The equivalent ground loop in proposed inverter topology 1 in Fig. 21(a)
Figure 2.33  Simulation results of ground loop voltage $V_{EG}$ in proposed inverter topology 1 in Fig. 21(a)

The output voltage and current of the proposed inverter are shown in Figure 2.23. The input dc voltage is 382.6V, the output ac voltage is 241.9V, and the output current is 1.01A.

As discussed in the Section I, high frequency common mode voltage and differential mode voltage need be well controlled to avoid the high frequency ground loop voltage on parasitic capacitor $C_{GP-V}$. The equivalent ground loop of the proposed inverter topology 1 is shown in Figure 2.23. The auxiliary switches $S_5$ and $S_6$ decouple the dc source from ac grid to minimize the ground loop common mode voltage. The ground loop CM voltage is the voltage between dc bus negative $G$ and ac grid ground $E$ ($V_{EG}$). The simulation results of the ground loop voltage $V_{EG}$ are shown in Figure 2.23, and the experimental results of ground loop voltage $V_{EG}$ are shown in Figure 2.23. Experiment result matches very well with the simulation results, and both of them show that the ground loop voltage $V_{EG}$ has a 60 Hz grid voltage component and a dc bias component.
It indicates nearly zero high-frequency voltage on the PV parasitic capacitor and associated leakage current. The waveform of $V_{EG}$ matches well with the equation (2.25) from the reference [49].

$$V_{EG} = (V_{dc} - V_{ac})/2$$  \hspace{1cm} (2.25)

In the experiment, YOKOGAWA WT1600 digital power meter is used to measure voltages, currents, and efficiency. The efficiency profile the proposed inverter is shown in Figure 2.23. The CEC efficiency is 98.51% for the proposed inverter topology 1 in Figure 2.23 (a). The calculated efficiency is also shown in Figure 2.23, which shows a significant difference in the lower power and medium power condition to the tested efficiency. Part of the efficiency difference comes from inaccurate calculation of the switching loss and inductor core loss.

![Figure 2.34 Calculated and test efficiency results under different power levels](image-url)
2.5 Inverter circuits with improved V-NPC technology for high input dc voltage application

2.5.1 Single-phase full bridge NPC inverter

The NPC half bridge inverter is widely used for high dc input voltage application. Due to its high DC voltage requirement, it usually need a boost converter for voltage boosting and is widely used in the single phase or three phase medium solar power inverters. The NPC half bridge inverter is shown in Figure 2.35, one terminal of grid voltage is connected to the DC bus voltage middle point, so the group loop voltage between the AC side ground (Point E) and DC side ground (Point G) is the voltage across the capacitor $C_4$, which is free of high frequency ripple. So high frequency ground loop leakage current will not be introduced with NPC half bridge inverter in PV system.

![Figure 2.35 The half bridge NPC inverter.](image)

Recent years, NPC bridge topology is adopt into the single-phase full bridge inverter. As shown in Figure 2.36, this single-phase full bridge inverter composes of two NPC half bridges, and a novel unipolar modulation is adopted to minimize the ground loop high frequency leakage current. The simplified
unipolar PWM implementation method and gating signals are shown in the Figure 2.37. The operation mode of this full bridge NPC inverter with the unipolar modulation is shown in Figure 2.38.

![Diagram of single-phase full bridge NPC inverter](image1)

**Figure 2.36** The single-phase full bridge NPC inverter.

![Diagram of PWM implementation and gating signals](image2)

**Figure 2.37** The PWM implementation method and gating signals for single-phase full bridge NPC inverter.

Figure 2.38 shows the four operating modes in one grid cycle for single-phase full bridge NPC inverter. In the positive half-line grid cycle, $S_1$ and $S_8$ are switched synchronously in high frequency PWM modulation; $S_2$ and $S_7$ are turned on. As shown in Figure 2.38(a), when $S_1$ and $S_8$ are turned on, the output
current goes through S₁, S₂, S₇ and S₈. As shown in Figure 2.38(b), when S₁ and S₈ are turned off, the freewheeling current goes through S₂, S₇, D₁, and D₄, and freewheeling circuit is clamped to the DC voltage middle point O. As shown in Figure 2.38(c), similarly, in the negative half line cycle, S₅ and S₄ are switched synchronously in the high frequency PWM modulation. When S₅ and S₄ are turned on, the output current goes through S₃, S₄, S₅ and S₆. As shown in Figure 2.38(d), when S₅ and S₄ are turned off, the freewheeling current goes through S₃, S₆, D₂, and D₃, and freewheeling circuit is clamped to the DC voltage middle point O.

![Operating modes of single-phase full bridge NPC inverter](image)

Figure 2.38 Operating modes of single-phase full bridge NPC inverter

54
2.5.2 Inverter circuit with V-NPC method

A novel single-phase full bridge inverter based on V-NPC method is proposed in Figure 2.39. Compared with full bridge NPC inverter in Figure 2.36, proposed inverter only need two power diodes. The PWM modulation is same with the traditional one, which is shown in Figure 2.37.
The operating model of this V-NPC technology based single-phase full bridge inverter is shown in Figure 2.40. As shown in Figure 2.40(a), when $S_1$ and $S_8$ are turned on, the output current goes through $S_1$, $S_2$, $S_7$ and $S_8$. As shown in Figure 2.40(b), when $S_1$ and $S_8$ are turned off, the freewheeling current goes through $D_5$. As shown in Figure 2.40(c), similarly, when $S_5$ and $S_4$ are turned on, the output current goes through $S_3$, $S_4$, $S_5$ and $S_6$. As shown in Figure 2.40(d), when $S_5$ and $S_4$ are turned off, the freewheeling current goes through $D_6$.

2.5.3 A family of inverter circuits with improved V-NPC method

Compared with the traditional full bridge NPC inverter, the proposed V-NPC based inverter topology only has two power diode, which means lower conduction loss, higher efficiency, and smaller package. But power circuit will not be clamped to a fixed power level during current freewheeling. In theoretically, if the power devices, gating voltages and gating speed are totally same and the power loop are perfect symmetrical, the power loop of proposed inverter during freewheeling will be clamped to the half of dc bus voltage. In practical, these condition cannot be guaranteed. In order to clamp the proposed inverter to a fixed power level during freewheeling, addition four clamping diodes (can be other clamping circuit) are added in to the proposed inverter, which is shown in Figure 2.41(a). these four clamping diode are just for power level clamping, should has no power consuming, and the package can be negligible compared with the power diode $D_5$ and $D_6$. Another three inverter
topologies based on improved V-NPC technology are also shown in Figure 2.42(b), Figure 2.42(c), and Figure 2.42(d).

A 300 W hardware prototype of the proposed inverter has been designed and tested. The DC input voltage is 380 Vdc, the AC output voltage is 240 Vac. The output voltage and output filter current waveforms are shown in the Figure 2.42. As shown in the Figure 2.42, the voltage stress of S1 is half of VDC; the drain voltage of the S3 is half of the VDC when the S1 is turned off, which means the power level is well clamped to DC bus middle point during the current freewheeling.
Figure 2.42 The output voltage, output current, and drain source voltage of devices
2.6 Summary

Compared with the traditional inverter with transformers, the transformerless inverter topology can achieve higher efficiency, smaller volume, and lower cost. For the high power and high input voltage application, the NPC topology is widely used. For the lower power and low input voltage single-phase transformerless inverter, there are a lot of new inverter topologies for better performance than traditional H-bridge inverter.

With the overview of the state-of-the-art transformerless inverter, a new inverter technology is summarized in this dissertation, which is the improvement of the traditional NPC technology and called V-NPC technology. Based on this new technology, a family of high-efficiency single-phase transformerless inverters are present in this dissertation. The PWM method and working principle are described, the circuit efficiency is also analyzed and tested with hardware prototype, which demonstrate the 98.96% peak efficiency at full load condition of 250W.

For the high dc input single-phase transformerless inverter, the V-NPC technology can be further improved. With the improved V-NPC technology, a family of single-phase inverters are proposed, experimental results also demonstrate the validity, and this can be an interesting topic for future work.
Chapter 3 MOSFET based Transformerless Inverter Circuit with High Magnetic Utilization

3.1 Introduction

In recent years, single-phase transformerless PV inverter products are becoming more and more popular. For efficiency consideration and standards compliance, a variety of inverter topologies have been adopted [32]-[61]. For the lower power level transformerless inverters, most of the innovative topologies use super junction metal oxide semiconductor field effect transistor (MOSFET) to boost efficiency [48]-[61].

The complimentary phase-leg with CoolMOS is shown Figure 3.1 (a). The super-junction metal oxide semiconductor field effect transistor’s (SJ-MOSFET or CoolMOS) voltage drop is resistive and is preferred for maintaining high efficiency under light-load conditions and also for fast switching speed. However, high-voltage CoolMOS suffers from slow reverse recovery of its snappy body diode, which not only produces high dv/dt, di/dt, and high power loss, but also creates phase-leg shoot through risk [84]-[89]. Therefore, high-voltage MOSFETs based phase-leg with top and bottom complimentary devices is not suitable for hard switching applications.

High efficiency power converters can be achieved by using CoolMOS and Silicon Schottky Carbide (SiC) diode. Typical examples are boost converters and buck converters (as shown in Figure 3.1(b)); in which, the snappy body diode will not conduct current under unidirectional current flowing. The reverse
recovery can be avoided with SiC diode, and high efficiency can be achieved with the high switching speed and low conduction loss of CoolMOS.

Figure 3.1 (a) Complimentary phase-leg with CoolMOS; (b) Buck converter with CoolMOS and SiC diode.

In the following, state-of-the-art MOSFET based transformerless inverter topologies will be reviewed and discussed according to their circuit topology, efficiency, MOSFET failure possibility from body diode reverse recovery, and magnetics utilization.

3.2 State-of-the-art MOSFET based transformerless inverters

3.2.1 Transformerless inverter with MOSFET phase-leg

As shown in the Figure 2.8, the HERIC inverter has the complimentary phase-leg, so device failure risk exists in phase leg when MOSFETs are adopted. Using MOSFETs in H-bridge (S1 to S4) for these topologies are prevented for commercial products. Commercial products obtains 97.8% peak efficiency for 5 kW inverter by using insulated gate bipolar transistor (IGBT) in HERIC topology [117]. Reference [79] uses the SiC-JFET to achieved 99% peak efficiency, however, it suffers from the high cost of devices
As shown in Figure 2.8, H5 topology of SMA [59], which only needs 3 MOSFETs and 2 IGBTs, decouples the PV panel from grid with two middle IGBTs during the current freewheeling period. The MOSFET failure risk from body diode reverse recovery can be eliminated by splitting MOSFET phase leg with two IGBTs. However, the conduction loss will be a little higher than HERIC topology due to 3 devices are in the conduction loop and fixed voltage drop of IGBTs.

As shown in Figure 2.8, H6 topology will still have complimentary phase-leg, so device failure risk exists in phase leg when MOSFETs are adopted. Besides, the symmetrical H6 topology in Figure 2.8 and hybrid phase-leg inverter topology in Figure 2.8 both have the complimentary phase-leg, so the high voltage MOSFETs are not suggested for these inverters.

As shown in Figure 3.2, the two stage topology with pseudo DC link, which can achieve high efficiency by adopting MOSFET in the first stage, operates S_5 and S_6 in high frequency and S_1 to S_4 in lower frequency. With proper operation of S_5 and S_6, system switching loss could be optimized. This method is adopted in the commercial product and obtains 98% peak efficiency and 97.5% CEC efficiency [40]. The drawbacks of this topology are still too many switches and high conduction loss (4 devices in conduction loop). The low frequency devices S_1 to S_4 also have diode reverse recovery risk during the current zero-crossing, and MOSFETs is not suggestion for S_1 to S_4.
3.2.2 Transformerless inverter without MOSFET phase-leg

With the poor reverse recovery from MOSFET’s slow body diode, MOSFET based phase-legs will have a risk of device failure, which is related to high $dv/dt$, $di/dt$ and phase-leg shoot through from gating voltage false triggering. As shown in Figure 3.1(b), if the inverter circuit doesn’t have the traditional complimentary phase-leg, high efficiency power converters can be achieved by using CoolMOS and Silicon Schottky Carbide (SiC) diode.

For the PV transformerless inverter application, an inverter circuit using non-complimentary phase-leg is shown in Figure 3.3, which can be named as dual buck transformerless inverter. This dual buck transformerless inverter is used in commercial product [111]. As shown in the Figure 3.3, the dual buck
inverter needs four CoolMOS and two Schottky diodes, and the CoolMOS phase leg is split into two independent buck converters by two filter inductors (S₁ and S₃ are split with Lᵢ₁; S₂ and S₄ are split with Lᵢ₂), so the body diode of CoolMOS will not conduct, and the reverse recovery issues can be avoided. In addition, this inverter can use unipolar modulation to achieve low common mode voltage. With CoolMOS / SiC-diode and unipolar modulation, the inverter can get 99% over a wide load range [41]. The major drawbacks of this inverter are (1) an additional large-size inductor, which has 50% the utilization because each inductor only conducts either positive or negative line cycle, and (2) it is not possible to realize reactive power generation because it only allows unidirectional power flow from dc to ac.

The bidirectional dual buck inverter [56], which is patented by Xantrex Technology Inc, provides another way for high reliability and high efficiency MOSFET inverter design. As shown in Figure 3.4, the dual buck inverter uses four output filter inductors to split the MOSFET phase legs. The snappy body diode of MOSFET will not conduct current under unidirectional current flowing. The reverse recovery can be avoided with SiC diode, and high efficiency can be achieved with the high switching speed and low conduction loss of CoolMOS. But this inverter needs to use bipolar modulation to minimize the common mode voltage for a transformerless inverter application [56], [66], [67]. Thus this inverter pays for its high reliability with lower efficiency and 50% magnetic utilization.
3.3 Proposed MOSFET based phase-leg method

Traditional MOSFET based phase leg has a risk of MOSFET failure, which is related to high dv/dt, high di/dt, over voltage of gating voltage, and phase leg shoot through by false triggering on during the body diode reverse recovery and is normally not suggested for high voltage hard-switching applications [84]-[89]. Figure 3.5(a) shows the traditional MOSFET phase leg. As shown in Figure 3.5 (b), by splitting the MOSFET phase leg into independent buck converters and boost converters with filter inductors, dual buck inverter disables the MOSFET body diodes. However, the magnetics are only 50% utilized.
Considering the MOSFET body diode reverse recovery risk in Figure 3.5 (a), and 50% magnetics utilization in Figure 3.5 (b), an improved circuit is proposed in Figure 3.5 (c). The basic idea of the proposed method is splitting the traditional MOSFET phase leg with a small phase-leg splitting inductor which serves two functions: the first function is disabling the MOSFET body diode by splitting the phase leg into an independent buck converter and boost converter under normal working conditions, and the second function is protecting MOSFETs by minimizing the \( \frac{di}{dt} \) and \( \frac{dv}{dt} \) even when an unexpected MOSFET body diode reverse recovery happens under abnormal conditions. The design of this phase-leg splitting inductor will be based on when MOSFET body diodes have reverse recovery under abnormal conditions, which can be output current is not well controlled in phase with grid voltage or sudden disturbance from grid side or dc input side.

In order to verify the proposed MOSFET based phase leg circuit under MOSFET body diode reverse recovery, two simulations are done in the SIMetrix by using the PSpice model of IPB60R099C6 \[125\]. The simulation adopts the double pulse method for device testing, which is shown in Figure 3.6. The dc voltage is 380 V, the inductor value is 4.5 mH, and the gating resistor is 4 Ω. In order to study the \( \frac{di}{dt} \) effect on gating voltage, a 5 nH common source inductance \( L_{CSI} \), which comes from the device lead and the printed circuit board trace, is introduced in the circuit \[84-86\]. By turning on the bottom MOSFET, the inductor current will be charged to about 0.7 A. Then by
turning off the bottom MOSFET, the inductor current will be forced to conduct through the top MOSFET's body diode. When the bottom MOSFET is turned on again, the top MOSFET's body diode will have a forced reverse recovery.

![Diagram](image)

**Figure 3.6 Double pulse test of the body diode reverse recovery**

The first simulation uses the phase leg shown in Figure 3.5(a) to study the MOSFET body diode reverse recovery effect. The waveforms during the forced reverse recovery are shown in Figure 3.7(a). The peak reverse recovery current is about 27.5 A under 0.7 A load current condition, and the di/dt of the recovery current is more than 1000A/µs. Both gate voltages see more than 40V, and both top and bottom MOSFETs experience false turn on and turn off, respectively. In this case, MOSFET failure will happen.

The second simulation uses the proposed phase leg with added phase-leg splitting inductor shown in Figure 3.5 (c). With a 38 µH inductor, the di/dt of the reverse current is only 10A/µs, and the peak reverse recovery current is less than 2.8 A under the same 0.7 A load current condition, as shown in Figure 3.7(b). The false turn on and shoot through failure are avoided in this case. The
selection criteria of phase-leg splitting inductor will be discussed in chapter 3.3.4.

Figure 3.7 Diode reverse recovery of IPB60R099C6 in (a) traditional phase leg (b) proposed phase leg.
3.4 Proposed transformerless inverter with proposed phase-leg

3.4.1 Proposed transformerless inverter circuit

Based on the proposed MOSFET phase leg method in Figure 3.5(c), this paper proposes a novel high efficiency MOSFET transformerless inverter. The diagram of proposed transformerless inverter with separated magnetics and integrated magnetics are shown in Figure 3.8(a) and Figure 3.8(b), respectively.

![Diagram of proposed transformerless inverter](image)

Figure 3.8 Proposed transformerless inverter topology with (a) separated magnetics (b) integrated magnetics

S₁, S₂, D₁, D₂, and L₀₁ make up one proposed phase leg and S₃, S₄, D₃, D₄, and L₀₄ make up another proposed phase leg; S₅ and D₅ provide a freewheeling loop for positive current; S₆ and D₆ provide a freewheeling loop for negative current. Phase-leg splitting inductors L₀₁ and L₀₄ can be coupled together and filter inductors L₀₂ and L₀₃ can be coupled together.
The phase-leg splitting inductors $L_{o1}$ and $L_{o4}$ have 50% utilization, but the filter inductors $L_{o2}$ and $L_{o3}$ have full utilization. The phase-leg splitting inductors $L_{o1}$ and $L_{o4}$ are only designed for $di/dt$ suppression with a value much smaller than the filter inductance. In this paper, the total inductance of phase-leg splitting inductor is 86 $\mu$H, and the filter inductors $L_{o2}$ and $L_{o3}$ are 4.7 mH. So even though the phase-leg splitting inductors only have 50% utilization, the overall inductance utilization is over 98%. Compared with inverter topologies in Figure 3.3 and Figure 3.4, whose magnetics only have 50% utilization, the proposed inverter almost achieves almost full utilization of magnetics. Thus the cost and volume of magnetics can almost be reduced by half. In addition, the proposed inverter still does not need PWM dead-time, only has two devices in the conduction loss, and has no risk from reverse recovery of MOSFET body diodes.

3.4.2 PWM method and operating modes

Figure 3.9 shows the PWM implementation circuit scheme for the proposed transformerless inverter. Figure 3.10 shows the PWM signals in time domain. In the positive half grid cycle, voltage reference signal $V_{\text{ref}}$ is compared with the carrier signal $V_{\text{carrier}}$, and the output signal is used to drive the devices $S_1$ and $S_4$, which are switched simultaneously in high frequency; voltage reference signal $V_{\text{ref}}$ is compared with 0 and outputs a high level signal to turn on $S_5$ in the entire positive grid cycle, which operates as a polarity selection in grid line frequency.
In the negative half grid cycle, the inverse signal of voltage reference $V_{\text{ref\_inv}}$ is compared with the carrier signal $V_{\text{carrier}}$, and the output signals are used to drive devices $S_2$ and $S_3$, which are switched simultaneously in high frequency; $S_6$ is turned on and operates as a polarity selection in grid line frequency. As one MOSFET is switching in high frequency, the other complimentary MOSFET in phase leg is in off-state, so all PWM signals do not need dead-time. This means duty cycle utilization is 100%.
Figure 3.11 shows the four operating modes in one grid cycle for the proposed inverter. In the positive half-line grid cycle, $S_1$ and $S_4$ are switched synchronously in high frequency PWM modulation; $S_5$ is turned on. As shown in Figure 3.11 (a), when $S_1$ and $S_4$ are turned on, $D_5$ is reverse-biased, the output current goes through $S_1$ and $S_4$. As shown in Figure 3.11 (b), when $S_1$ and $S_4$ are turned off, $D_5$ is forward-biased and the freewheeling current goes through $S_5$ and $D_5$. In the positive half line cycle, both filter and phase-leg splitting inductors conduct current.

Similarly, in the negative half line cycle, $S_2$ and $S_3$ are switched synchronously in the high frequency PWM modulation; $S_6$ is turned on. As shown in Figure 3.11 (c), when $S_2$ and $S_3$ are turned on, $D_6$ is reverse-biased, the output current goes through $S_2$ and $S_3$. As shown in Figure 3.11 (d), when $S_2$ and $S_3$ are turned off, $D_6$ is forward-biased and the freewheeling current goes through $S_6$ and $D_6$. In the negative half line cycle, phase-leg splitting inductors do not need to conduct. Therefore, the phase-leg splitting inductors have 50% utilization, but filter inductors are fully utilized.
Figure 3.11 Operating modes of the proposed transformerless inverter: (a) Positive half-line cycle, $S_1$ and $S_4$ are on, (b) Positive half-line cycle, $S_1$ and $S_4$ are off, free-wheeling current goes through $S_5$ and $D_5$, (c) Negative half-line cycle, $S_3$ and $S_2$ are on, (d) Negative half-line cycle, $S_3$ and $S_2$ are off, free-wheeling current goes through $S_6$ and $D_6$. 
3.4.3 Ground loop voltage analysis

In the transformerless PV inverter system, there is a parasitic capacitance exists between the PV array cells and the metal frame [62-74]. The PV array cells are connected to the dc bus (point G in Figure 3.12); the PV metal frame is still grounded (point E in Figure 3.12). So this parasitic capacitance, which is referred as $C_{G\text{-PV}}$ in the Figure 3.12, will exist in the ground loop. If the high frequency common mode voltage (CM) voltage and differential mode (DM) voltage are not well controlled, there will be a high frequency ground loop voltage on this parasitic capacitor, and high frequency leakage current will be generated in turn. This leakage current can cause distortion and harmonic, high losses, safety issue, fault protection and electron magnetic interference. The requirements for limiting ground loop leakage current and fault current can be referred to VDE0126-1-1, and UL 1741[27], [28]. If inverter circuit and PWM modulation are not well designed, bulk CM filter and DM filter are need to minimize the ground loop CM voltage. If the ground loop CM voltage is free of high frequency voltage component, the CM filter and DM filter can be minimized designed to reduce the size and cost. This Section will analyze the ground loop voltage of improved inverter under proposed PWM modulation method. Analysis results will guide the circuit components design for low ground loop CM voltage.
During the positive half cycle, the output terminals of the switch phase legs are $V_1$ and $V_4$, respectively. The diagram of the simplified circuit with CM and DM model during the positive half-line grid cycle is shown in Figure 3.13.

When $S_1$ and $S_4$ are turned on, $V_1$ equals to $V_{dc}$, $V_4$ equals to zero if $G$ is set as zero reference. According to the definition of CM voltage and DM voltage, the CM and DM voltages in the positive half cycle are:

$$V_{CM-P_{on}} = \frac{V_1 + V_4}{2} = \frac{V_{dc}}{2}$$  \hspace{1cm} (3.1)$$

$$V_{DM-P_{on}} = V_1 - V_4 = V_{dc}$$  \hspace{1cm} (3.2)$$
\[ V_{EG-P_{on}} = V_{4G} + V_{EV4} \]
\[ = V_{CM-P_{on}} - 0.5V_{DM-P_{on}} + \frac{(V_{DM-P_{on}} - V_{ac}) \cdot (L_{o3} + L_{o4})}{L_{o1} + L_{o2} + L_{o3} + L_{o4}} \]  
\[ (3.3) \]

As shown in Figure 3.13, the voltage \( V_{EG} \) has three components. The first one is from the DM voltage of the switch phase legs, the second one is from the DM voltage of the grid voltage \( V_{ac} \), and the third one is from the CM voltage of the switch phase legs. The voltage \( V_{EG} \) in the positive line cycle with switches on is given in (3.3).

As shown in Figure 3.12 (b), in the positive half-line grid cycle, when \( S_1 \) and \( S_4 \) are turned off, the free-wheeling current goes through \( S_5 \) and \( D_5 \). The CM and DM voltages in the circuit are:

\[ V_{CM-P_{off}} = \frac{V_1 + V_4}{2} = \frac{V_{dc}}{2} \]  
\[ (3.4) \]

\[ V_{DM-P_{off}} = V_1 - V_4 = 0 \]  
\[ (3.5) \]

\[ V_{EG-P_{off}} = V_{CM-P_{off}} - 0.5V_{DM-P_{off}} + \frac{(V_{DM-P_{off}} - V_{ac}) \cdot (L_{o3} + L_{o4})}{L_{o1} + L_{o2} + L_{o3} + L_{o4}} \]  
\[ = 0.5V_{dc} + \frac{-V_{ac} \cdot (L_{o3} + L_{o4})}{L_{o1} + L_{o2} + L_{o3} + L_{o4}} \]  
\[ (3.6) \]

The voltage \( V_{EG} \) in the positive line cycle with switches \( S_1 \) and \( S_4 \) off is given in (3.6).

During the negative half cycle, the output terminals of switch phase legs are \( V_2 \) and \( V_3 \), respectively. The diagram of the simplified circuit with CM and DM model during the negative half-line grid cycle is shown in Figure 3.14. When
S2 and S3 are turned on, V3 equals to Vdc, V2 equals to zero if G is set as zero reference.

When the S2 and S3 are turned on, the CM and DM voltage are:

\[ V_{CM-N_{on}} = \frac{V_3 + V_2}{2} = \frac{V_{dc}}{2} \]  \hspace{1cm} (3.7)

\[ V_{DM-N_{on}} = V_3 - V_2 = V_{dc} \]  \hspace{1cm} (3.8)

\[ V_{EG-N_{on}} = V_{3G} + V_{E-V3} \]

\[ = V_{CM-N_{on}} + 0.5V_{DM-N_{on}} - \frac{(V_{DM-N_{on}} + V_{ac}) \cdot L_{o3}}{L_{o2} + L_{o3}} \]  \hspace{1cm} (3.9)

\[ = V_{dc} - \frac{(V_{dc} + V_{ac}) \cdot L_{o3}}{L_{o2} + L_{o3}} \]

The voltage \( V_{EG} \) in the negative line cycle with switches S2 and S3 on is given in (3.9):

![Figure 3.14 Equivalent circuit with CM and DM model for the negative half-line cycle](image)

As shown in Figure 3.12 (d), in the negative half-line grid cycle, when S2 and S3 are turned off, the free-wheeling current goes through S6 and D6. The CM and DM voltages in the circuit are:
\[ V_{CM-N_{off}} = \frac{V_3 + V_2}{2} = \frac{V_{dc}}{2} \]  
\[ V_{DM-N_{off}} = V_3 - V_2 = 0 \]

The voltage \( V_{EG} \) in the negative line cycle with switches \( S_2 \) and \( S_3 \) off is given in (3.12).

\[
V_{EG-N_{off}} = V_{CM-N_{off}} + 0.5V_{DM-N_{off}} + \frac{(V_{DM-N_{off}} - V_{ac}) \cdot L_{o3}}{L_{o2} + L_{o3}} = 0.5V_{dc} + \frac{-V_{ac} \cdot L_{o3}}{L_{o2} + L_{o3}}
\]

In the proposed inverter, if the inductance \( L_{o2} \) and \( L_{o3} \) have the same value and \( L_{o1} \) and \( L_{o4} \) have the same value, \( V_{EG} \) comes out to be the same in four different operating modes according to (3.3), (3.6), (3.9), and (3.12), that is:

\[
V_{EG-P_{on}} = V_{EG-P_{off}} = V_{EG-N_{on}} = V_{EG-N_{off}} = \frac{V_{dc} - V_{ac}}{2}
\]

If the phase-leg splitting inductors (\( L_{o1} \) and \( L_{o4} \)) or filter inductors (\( L_{o2} \) and \( L_{o3} \)) are not symmetrically designed, the DM and CM voltages will bring high frequency voltage to \( V_{EG} \). In order to minimize the high frequency leakage current, \( L_{o2} \) and \( L_{o3} \) are designed with one coupled inductor, \( L_{o1} \) and \( L_{o4} \) are designed with another coupled inductor, which allows a better matching between \( L_{o2} \) and \( L_{o3} \) and between \( L_{o1} \) and \( L_{o4} \). As a result, the voltage \( V_{EG} \) will be a line frequency sinusoidal voltage with a dc offset, which is shown in (3.13). The experimental \( V_{EG} \) waveform will be shown in Part VI, which should verify the validity of the analysis in this section.
3.4.4 Component selection and loss analysis

The output filter of this inverter design is based on the maximum ripple current. As shown in (3.14), the maximum ripple current is usually designed to be around 10% to 30% of rated current, which is about 1.04 A (1.47 A peak value) for 240 V output voltage and 250 W rated output power. The ripple current is a function of dc voltage, ac grid voltage, filter inductor value, and PWM turn on time, which is presented in (3.15).

\[
\Delta i_{\text{ripple}} \leq (10\% \sim 30\%) \cdot I_{\text{rated}} \tag{3.14}
\]

\[
2\Delta i_{\text{ripple}} = \frac{(V_{dc} - V_{ac})}{L_{\text{filter}}} \cdot T_{on} = \frac{(V_{dc} - D \cdot V_{dc})}{L_{\text{filter}}} \cdot \frac{D}{f_{sw}} \tag{3.15}
\]

The proposed inverter is designed to work at 30 kHz switching frequency, and the inverter output filter inductor is designed to have 25% maximum current ripple, which is 0.37 A. The maximum current ripple happens at duty cycle equals to 0.5. Through (3.15), the output filter inductance is calculated to be 4.3 mH.

RM 14 low profile magnetic cores with N95 ferrite material from EPCOS are selected for the output filter [123]. Proper gap \( l_{\text{gap}} \) is used to prevent the maximum flux density \( B_{\text{max}} \) from saturating under the maximum current condition. The relationship of maximum flux density with turns \( N \), maximum current \( I_{\text{max}} \), and gap is shown in (3.16). The relationship between inductance value \( L_{\text{filter}} \) and gap distance is shown in (3.16). Finally, 4.3 mH inductance is achieved through 91 turns, which can achieve 23% maximum current ripple.
\[ B_{\text{max}} \approx \frac{N \cdot I_{\text{max}}}{I_{\text{gap}}} \]  \hspace{1cm} (3.16)

\[ L_{\text{filter}} = \frac{N^2}{I_{\text{gap}}} \left( \frac{1}{u_0 A_e} + \frac{1}{u_i A_e} \right) \approx \frac{N^2}{I_{\text{gap}}} \]  \hspace{1cm} (3.17)

The filter capacitor design is based on the cut-off frequency of the output filter, which is usually around 10% to 20% of the switching frequency, the selection of filter capacitor can follow (3.18). The 0.47 µF capacitor is selected as the output filter capacitor for the 30 kHz switching frequency in proposed inverter, which achieves 3.4 kHz cut-off frequency with the filter inductor.

\[ \frac{1}{2\pi \sqrt{L_{\text{filter}} \cdot C_{\text{filter}}}} \leq (10\% \sim 20\%) \times f_{\text{sw}} \]  \hspace{1cm} (3.18)

As mentioned in the Chapter 3.3, the design of phase-leg splitting inductor \( L_{01} \) and \( L_{04} \) should be based on the worst condition. The worst condition is when the top MOSFET \( S_1 \) and bottom MOSFET \( S_2 \) have a hard commutation through \( L_{01} \).

The design criterion of phase-leg splitting inductor is mainly to set the limit of the \( \text{di/dt} \) for the MOSFET body diode reverse recovery current under abnormal conditions to avoid false turn on and partial shoot through. For the selected MOSFET IPB60R099C6 [125], as shown in Figure 3.7 (b), the gate plateau voltage is around 5.4 V, therefore, the phase-leg splitting inductor should be large enough to ensure the gating spike or noise voltage well below the plateau voltage. In this paper, a peak gating voltage of 2.7 V is selected as
the design target for 100% margin. To achieve this target, one can perform the
circuit simulation with actual device model or through try-and-error
experiments. This paper uses PSpice model of IPB60R099C6 in SIMetrix
circuit simulator with the double pulse simulation to determine the di/dt that
limits the peak gating spike or noise voltage to below 2.7 V. Simulation results
in Figure 3.7(b) indicated that di/dt should be less than 10A/us to achieve the
design target. Thus, the minimum value of phase-leg splitting inductor $L_{min}$
can be formulated as follows.

$$L = \frac{\Delta V}{\Delta i} = \frac{V_{dc}}{\Delta i} \frac{\Delta i}{\Delta t}$$ (3.19)

$$L_{min} \geq \frac{V_{dc}}{|di/dt|_{max}}$$ (3.20)

With 10A/us as the maximum di/dt limit, the minimum inductor comes out
to be 38 µH for 380 Vdc through(3.20). The final implementation adopts two
molypermalloy powder cores (#55035) in stack, which yields 43 µH inductance
with 16 turns for each phase-lag splitting inductor.

During the normal condition, four diodes D_1 to D_4 only serve as the
clamping diodes and they do not conduct current. MURA160T3G (600V, 2A;
surface mount package DO-214) is chosen for these clamping diodes. Diodes D_5
and D_6 need to conduct the freewheeling current and withstand the hard
commutating when S_1-S_4 (or S_2-S_3) are turned on. C3D10060G (600V, SiC
diode)[130], which has no reverse recovery loss during switching, is chosen for
D_5 and D_6. For all main devices, S_1 to S_6, IPB60R099C6 is selected.
The losses in the power circuit can be divided into the conduction loss (power device conduction loss and inductor conduction loss), switching loss, and inductor core loss.

The voltage drop of MOSFETs can be simplified as a channel resistor, the voltage drop of diodes can be simplified as a voltage source series with a channel resistor, which are shown in the flowing respectively.

\[ V_{ds} = i \cdot R_{ds} \]  \hspace{1cm} (3.21)

\[ V_{ak} = V_f + i \cdot R_{ak} \]  \hspace{1cm} (3.22)

For the positive half cycle, the duty cycle of \( S_1 \), \( S_4 \) can be expressed as (3.23).

The duty cycle of the MOSFET \( S_5 \) can be expressed as (3.24). The power losses on \( S_2, S_3, \) and \( S_6 \) in the negative half cycle are the same due to the symmetric operation modes.

\[ d_{S_1S_\bar{1}} = m \cdot \sin(\omega t) \]  \hspace{1cm} (3.23)

\[ d_{S_5} = 1 \cdot m \cdot \sin(\omega t) \]  \hspace{1cm} (3.24)

Assuming the output current is in-phase with the duty cycle, which means the pure active generation condition, the output current can be expressed as:

\[ i(t) = I_m \cdot \sin(\omega t) \]  \hspace{1cm} (3.25)

The current in the power device is PWM current, whose conduction time depends on the duty cycle condition. All the power devices will only work for half of the line cycle, the conduction losses on high frequency MOSFETs (\( S_1 \) to \( S_4 \)), line frequency MOSFETs (\( S_5, S_6 \)), and freewheeling Diodes (\( D_5, D_6 \)) are
given in (3.26), (3.27), and (3.28). The total conduction loss of all devices is given in (3.29).

\[
P_{\text{HighFrequency\_MOSFET}} = \frac{1}{2\pi} \int_{0}^{\pi} i(t) \cdot v_{ds}(t) \cdot d_{\text{active}}(t) \cdot d(\omega t)
\]
(3.26)

\[= I_m^2 \cdot R_{ds} \cdot \frac{2M}{3\pi}
\]

\[
P_{\text{LowFrequency\_MOSFET}} = \frac{1}{2\pi} \int_{0}^{\pi} i(t) \cdot v_{ds}(t) \cdot d_{\text{zero}}(t) \cdot d(\omega t)
\]
(3.27)

\[= I_m^2 \cdot R_{ds} \cdot \left(\frac{1}{4} - \frac{2M}{3\pi}\right)
\]

\[
P_{\text{Diode}} = \frac{1}{2\pi} \int_{0}^{\pi} i(t) \cdot v_{ak}(t) \cdot (1-M\sin(\omega t)) \cdot d(\omega t)
\]
(3.28)

\[= I_m \cdot V_f \cdot \left(\frac{1}{\pi} - \frac{M}{4}\right) + I_m^2 \cdot R_{ak} \cdot \left(\frac{1}{4} - \frac{2M}{3\pi}\right)
\]

\[
P_{\text{cond}} = 4P_{\text{HighFrequency\_MOSFET}} + 2P_{\text{Diode}} + 2P_{\text{LowFrequency\_MOSFET}}
\]

\[= 4I_m^2 \cdot R_{ds} \cdot \frac{2M}{3\pi} + 2I_m \cdot V_f \cdot \left(\frac{1}{\pi} - \frac{M}{4}\right) + 2I_m^2 \cdot R_{ak} \cdot \left(\frac{1}{4} - \frac{2M}{3\pi}\right) + 2I_m^2 \cdot R_{ds} \cdot \left(\frac{1}{4} - \frac{2M}{3\pi}\right)
\]
(3.29)

The calculation method of inductor core loss, conduction loss, devices switching loss is as same as the method in chapter 2.4.3.

As the CEC efficiency is weighted efficiency calculated at 10%, 20%, 30%, 50%, 75%, and 100% of the full power level. The power losses of the proposed inverter circuit are calculated at 10%, 20%, 30%, 50%, 75%, and 100% of the full power level at 250 W, and individual power losses under different power levels are shown in the Figure 3.15. The calculated total loss under different power levels and related system efficiency are shown in Figure 3.16.
Figure 3.15 Calculated individual power loss under different power levels.

Figure 3.16 Calculated total loss and efficiency under different power levels.

3.4.5 Experimental results

A 250 W micro-inverter hardware prototype with 380 V dc input and 240 V ac output has been designed, fabricated and tested in the two stage non-isolated micro-inverter to verify the validity of the proposed high efficiency MOSFET transformerless inverter. The prototype of the two stage non-isolated micro-inverter is shown in Figure 3.17, which can be divided into the high boost ratio non-isolated DC-DC converter and the proposed transformerless inverter.
Figure 3.17 250W two stage non-isolated micro-inverter hardware prototype.

As shown in Figure 3.17, Phase-leg splitting inductors only conduct in positive half line cycle and have 50% utilization, but filter inductors have full utilization. Compared with filter inductors, the phase-leg splitting inductors are much smaller. The output filter inductor is 4.3 mH with the weight 90 g, the phase-leg splitting inductor is 0.086 mH in total with the weight 4 g. Compared with transformerless MOSFET inverter topologies in Figure 3.3 and Figure 3.4, which only have 50% utilization of magnetics, the proposed transformerless MOSFET inverter has 98% utilization of inductance value and 96% utilization of weight.
The output voltage and current waveforms of the proposed inverter are shown in Figure 3.18. As there is no dead-time requirement for each PWM switching cycle, the proposed inverter has no duty cycle loss, which means 340 V dc bus can almost generate 240 V ac sinusoid voltage.

Figure 3.19 shows the gating signals for all switches. In the positive half cycle, $S_1$ and $S_4$ are switched simultaneously in high frequency PWM and $S_5$ is always on; other switches are always off. In the negative half cycle $S_2$ and $S_3$
are switched simultaneously in high frequency PWM and \( S_6 \) is always on; other switches are always off.

Figure 3.20 Inverter splitting inductor current waveform.

Figure 3.21 Waveforms of Voltage between grid ground and DC ground (\( V_{EG} \))

As shown in Figure 3.20, the splitting inductors \( L_{01} \) and \( L_{04} \) only conduct current in the positive half cycle. The voltage between dc bus negative G and ac grid ground E (\( V_{EG} \)) is shown in Figure 3.21, which has a 60 Hz grid voltage component and a dc bias component. The waveform of \( V_{EG} \) matches well with
the calculation results in the (12). This indicates nearly zero high-frequency voltage on the PV parasitic capacitor, which means minimized leakage current.

Figure 3.22 Efficiency test results of 250W proposed inverter.

In the experiment, YOKOGAWA WT1600 digital power meter is used to measure voltages, currents, and efficiency [131]. The efficiency measurement is based on measuring the inverter output ac power and the inverter dc input power. The efficiency measurement only involves the power stage loss, not including auxiliary power supply and DSP power losses. The test efficiency and the calculated efficiency of proposed inverter are shown in Figure 3.22, which shows 99.01% peak efficiency at full load 250 W. The CEC efficiency is a weighted efficiency calculated at 10%, 20%, 30%, 50%, 75%, and 100% of the full power level [25]. The overall CEC efficiency of proposed inverter power stage is 98.8%, which is calculated through:
$$\eta_{CEC} = 0.04\eta_{10\%} + 0.05\eta_{20\%} + 0.12\eta_{30\%} + 0.21\eta_{50\%} + 0.53\eta_{75\%} + 0.05\eta_{100\%}$$

(3.30)

3.5 General applications of proposed MOSFET based phase-leg

The proposed transformerless inverter in Chapter 3.4.1 is just one application of the proposed MOSFET based phase-leg. Proposed MOSFET based phase-leg can be applied into almost all the transformerless inverters to use MOSFETs to replace IGBTs. The Figure 3.23 shows the NPC inverter topology with proposed MOSFET based phase-leg; the Figure 3.23 shows the T-type inverter topology with proposed MOSFET based phase-leg; the Figure 3.23 shows the H-type inverter topology with proposed MOSFET based phase-leg; the Figure 3.23 shows the H-bridge inverter topology with proposed MOSFET based phase-leg; the Figure 3.23 shows the H5 inverter topology with proposed MOSFET based phase-leg; the Figure 3.23 shows the H6 inverter topology with proposed MOSFET based phase-leg; the Figure 3.23 shows the asymmetry H6 inverter topology with proposed MOSFET based phase-leg.

(a) NPC topology  
(b) NPC topology with proposed phase-leg

Figure 3.23 Application of proposed MOSFET phase-leg on NPC topology
(a) T-type inverter topology      (b) T-type inverter topology with proposed phase-leg

Figure 3.24 Application of proposed MOSFET phase-leg on T-type inverter

(a) H-bridge topology      (b) H-bridge topology with proposed phase-leg

Figure 3.25 Application of proposed MOSFET phase-leg on H-bridge topology

(a) H5 topology      (b) H5 topology with proposed phase-leg

Figure 3.26 Application of proposed MOSFET phase-leg on H5 topology
3.6 Summary

Most of the innovative transformerless inverter topologies use super junction metal oxide semiconductor field effect transistor (MOSFET) to boost efficiency. However, these MOSFET based inverter topologies suffer from one or more of these drawbacks: MOSFET failure risk from body diode reverse recovery, increased conduction losses due to more devices, or low magnetics utilization.
With the review of the state-of-the-art low power level MOSFET based transformerless photovoltaic inverters, the inverter topologies can be divided into with MOSFET phase-leg and without MOSFET phase-leg. The MOSFET phase-leg has the issue of body diode reverse recovery, the inverter without MOSFET phase-leg need to use filter inductor to splide the original MOSFET phase. Based on these analysis, a novel MOSFET phase-leg method is proposed.

Based on the proposed phase leg configuration, a high efficiency single-phase MOSFET transformerless inverter is presented for the PV micro-inverter applications. The PWM modulation and circuit operation principle are then described. The common mode and differential mode voltage model is then presented and analyzed for circuit design. Experimental results of a 250 W hardware prototype are shown to demonstrate the merits of the proposed transformerless inverter topology.

The proposed transformerless inverter is just the application of proposed MOSFET based phase-leg on HERIC inverter. Proposed MOSFET based phase-leg can be application into almost all the transformerless inverters, and the application on some typical inverters are shown in the Chapter 3.5, which will be an interesting research topic for future work.
Chapter 4 Reactive Power Generation on MOSFET Based Transformerless Inverter

4.1 Introduction

With more and more PV installations, the PV output create a significant impact to the entire power grid [7]-[10]. As shown in Figure 4.1, without PV generation, the power flowing in the distribution system is unidirectional, and the power line voltage will continue dropping as the line distance increases. In order to maintain the lowest consumer voltage to be above the low threshold voltage at high load condition, the voltage on the substation transformer side is normally set higher in the existing grid system such that the customers with

Figure 4.1 Power line voltage distribution in PV generation system with/without reaction power compensation of PV inverters.
long distance from substation can maintain a reasonable voltage under heavy load conditions.

Without PV feed-in, the pink dotted line (Case 1) in Figure 4.1 indicates that the voltage level reduces as the distance increases. With PV generation, the power flowing in the distribution system can be bi-directional. If a large number of PV inverters are installed, and significant active power is fed into grid, the voltage can increase even with long line distance. In some cases, the customer side voltage may exceed the upper threshold voltage, as shown in red dashed line (Case 2) of Figure 4.1. One way to resolve this over voltage is to limit the PV output power, and the other way is to use the cost free PV inverters to regulate the voltage by absorbing reactive power. The line voltage distribution of the high PV feed-in with reactive power compensation is described with a blue solid line (Case 3) in Figure 4.1.

Voltage sags and swells can also happen with unsupported load or sudden load changes. With reactive power control of PV inverters, the voltage fluctuations can be mitigated, and system interruption can be avoided. Avoiding unnecessary interruption implies the improvement of the grid’s stability, reliability, quality, and efficiency [7]-[10]. In order to fully utilize the PV inverter capability, IEEE 1547a [29] and The California’s Electric Tariff Rule 21 [30] are proposing the roles of the distributed energy resource systems including PV generation. The main requirements of upcoming standards in USA for PV inverters are summarized as:

94
1. Providing reactive power with a fixed power factor.
2. Providing dynamic reactive power injection through autonomous responses to local voltage measurements.

So, PV inverters need to have reactive power capability in the future.

![Figure 4.2 Four different regions in time domain under current lagging condition](image)

According to the direction of the inverter output voltage and output current, the inverter work condition under reactive power generation can be divided into four different regions, The sequence of four different regions under the current lagging (overexcited power factor or generating reactive power) condition in one line cycle is shown in Figure 4.2.

As shown in Figure 4.2, four different regions that can be defined as region I: inverter output voltage and output current are both positive, energy is transferred from dc side to ac grid side, and inverter should be operated under buck mode.

Region II: inverter output voltage is negative and output current is positive, energy is transferred from ac side to dc side, and inverter should be operated under boost mode.
Region III: inverter output voltage and output current are both negative, energy is transferred from dc side to ac grid side, and inverter should be operated under buck mode.

Region IV: inverter output voltage is positive and output current is negative, energy is transferred from ac side to dc side, and inverter should be operated under boost mode.

For the inverter circuit, the bidirectional current flowing capability is requirement for the reactive power generation.

4.2 Reactive power capability for current MOSFET based transformerless inverters

For the transformerless inverter topology, some topology use the traditional complimentary phase-leg method. In this configuration, the high-voltage MOSFET will suffers from slow reverse recovery of its snappy body diode, which not only produces high dv/dt, di/dt, and high power loss, but also creates phase-leg shoot through risk [84]-[89]. Therefore, high-voltage MOSFETs based phase-leg with top and bottom complimentary devices is not suitable for hard switching applications. The bidirectional phase-leg with complimentary MOSFET is shown in Figure 4.3 (a).

Some transformerless inverter topologies are based on the unidirectional buck method, which is shown in Figure 4.3 (b). In this topology, the snappy body diode will not conduct current under unidirectional current flowing. The reverse recovery can be avoided with SiC diode, and high efficiency can be
achieved with the high switching speed and low conduction loss of MOSFET. But these topologies only support unidirectional current flowing, so they will not have reactive power generation capability.

Some transformerless inverter topologies are based on the bidirectional buck method, which is shown in Figure 4.3 (c). In this topology, the snappy body diode will not conduct current under unidirectional current flowing for each single channel, so MOSFET ad SiC diode can be adopted for high efficiency. This topology can also do reactive power generation due to this topology support the bidirectional current flowing.

![Figure 4.3 MOSFET phase leg configurations](image)

(a) (b) (c)

Figure 4.3 MOSFET phase leg configurations: (a) Traditional phase-leg method, (b) unidirectional buck method, (c) Bidirectional buck method.

4.2.1 High efficiency topologies suffer from MOSFET body diode reverse recovery for reactive power generation

The HERIC inverter, H5 inverter, H6 inverter, hybrid phase-leg inverter topologies and so on all base on the traditional complimentary phase-leg method, which is shown in Figure 4.3 (a). So these inverter topologies will suffer from the MOSFET body diode reverse recovery for reactive power generation.
as high $dv/dt$, $di/dt$, and high power loss, and possible phase-leg shoot through issues, commercial product use the IGBTs for the reactive power generation.

![Diagrams](image)

(a). The HERIC inverter topology  (b). The H5 inverter topology

c. The H6 inverter topology  (d). The hybrid bridge inverter topology

**Figure 4.4** High efficiency transformerless inverter suffer MOSFET body diode reverse recovery for reactive power generation

### 4.2.2 High efficiency MOSFET inverters don’t support reactive power generation

As shown in Figure 4.5, the dual back inverter and two stage inverter topology all base on the unidirectional buck converter method, which is shown in Figure 4.3 (b). So the MOSFET body diode in these inverter topologies will not conduction, and high efficiency power conversion can be achieved through MOSFET, SiC diode, and the unipolar PWM method. These topologies only have unidirectional current flow with buck circuit, so it is impossible to do reactive power generation. Besides, only half of the inductors are used in each
half line cycle, so the magnetic utilization is low. So the major drawbacks of this inverter are (1) an additional large-size inductor, which has 50% the utilization because each inductor only conducts either positive or negative line cycle, and (2) it is not possible to realize reactive power generation because it only allows unidirectional power flow from dc to ac.

4.2.3 MOSFET inverter support reactive power generation

Another MOSFET based inverter is bidirectional dual buck inverter, which is patented by Xantrex Technology Inc, provides another way for high reliability and MOSFET based inverter design [56]. As shown in Figure 4.6, the bidirectional dual buck inverter uses four output filter inductors to split the MOSFET phase legs and also needs to use bipolar modulation to minimize the common mode voltage for a transformerless inverter application [49], [50]. With four output filter inductor for phase-leg splitting, only half of the inductors will be utilized for each half of the line cycle: with the bipolar modulation, the efficiency will be reduced compared to the unipolar...
modulation. Thus this bidirectional dual buck inverter pays for its high reliability with lower efficiency and 50% magnetic utilization.

![Figure 4.6 MOSFET based inverter support reactive power generation](image)

### 4.2.4 A improved MOSFET inverter for reactive power generation

In summary, state-of-the-art transformerless inverters have trade-offs in one or more of the following: (1) suffering from MOSFET body diode reverse recovery for reactive power generation; (2) inverter circuit only support unidirectional current flowing and doesn’t support reactive power generation; (3) can use MOSFET support reactive power generation, but suffer from lower efficiency with bipolar modulation and lower magnetic utilization.

A high-efficiency single-phase CoolMOS/SiC-diode based transformerless PV inverter has been proposed in [49]. The key to achieve high efficiency secret for this inverter is as same as that of the dual buck transformerless inverter in Figure 4.5 and Figure 4.6, in which a small phase-leg splitting inductor $L_{ph}$ is adopted to split the MOSFET phase-leg into an independent buck converter and boost converter to disable the MOSFET body diode. This method avoids the MOSFET body diode reverse recovery.
Compared with the bidirectional dual buck inverter in Figure 4.6, the high-efficiency single-phase CoolMOS/SiC-diode based transformerless inverter not only has high circuit efficiency with unipolar PWM method, but also has high magnetic utilization. The inverter phase-leg is shown in Figure 4.7. The CoolMOS/SiC-diode based inverter in [49] is shown in Figure 4.8.

Figure 4.7 MOSFET based Phase-leg method

Figure 4.8 Improved CoolMOS/SiC-diode based transformerless inverter

Single-phase transformerless inverter in [49] only supports unity power factor operation and has 3 limitations for reactive power generation. The first limitation is the diodes $D_1$ through $D_4$ in the circuit proposed are small clamping diodes $D_1$ through $D_4$, which can only support unity power factor condition. The second limitation is the circuit operating modes for reactive power generation is not described, which should contain the ac to dc boost operation mode for reactive power generation. The third limitation is it is not
capable of reactive power generation with the PWM modulation method proposed in [49], or the traditional unipolar or bipolar modulation method.

The first limitation of the circuit proposed in [49] is the use of small clamping diodes $D_1$ through $D_4$, which can only support unity power factor condition (clamping diodes don’t conduct current, are not power diode). In this paper, these clamping diodes are replaced with Schottky power diodes and will conduct current when energy is transferred from ac grid side to dc side. As shown in Figure 4.8, with the using of Schottky diodes, the improved circuit would allow non-unity power factor power flowing.

4.3 Operating modes of the improved MOSFET based transformerless inverters

The second limitation of the improved single-phase CoolMOS/SiC-diode based transformerless inverter is the circuit operating modes for reactive power generation is not described, which should contain the ac to dc boost operation mode for reactive power generation. Based on the analysis in chapter 4.1, four different inverter circuit operating modes for four different regions will be proposed in this part.

When the grid voltage and the inverter output current are both positive, the inverter works in region I. The inverter circuit will be operated in buck mode with $S_1$, $S_4$ and $S_5$. $S_1$ and $S_4$ switch simultaneously in high frequency; $S_5$ remains on during this region. The inverter circuit operating mode is shown in Figure 4.9. As shown in Figure 4.9 (a), when $S_1$ and $S_4$ are turned on, $D_5$ will
be turned off, the energy will be transferred from dc to ac grid. As shown in Figure 4.9 (b), when $S_1$ and $S_4$ are turned off, and freewheeling current will go through $S_5$ and $D_5$. In this buck operating mode, $S_1$ and $S_4$ are the active switches, $D_5$ is the freewheeling diode.

![Figure 4.9 Buck operating mode in the I region](image)

When the grid voltage is negative and the output current is positive, inverter works in region II. The inverter circuit will be operated in boost mode with $S_5$. Switch $S_5$ operates in high frequency, and $D_1$ and $D_4$ are the freewheeling diodes. The inverter operating mode is shown in Figure 4.10. As shown in Figure 4.10 (a), when $S_5$ is turned on, diodes $D_1$ and $D_4$ will be turned off, ac grid voltage will charge the filter inductors. In Figure 4.10 (b), when $S_5$ is turned off, freewheeling current will go through diodes $D_1$ and $D_4$, and the
energy will be transferred from ac side to dc side. In this boost operating mode, $S_5$ is the boost active switch, $D_3/D_4$ are the freewheeling diodes.
When the grid voltage and the output current are both negative, the inverter works in region III. The inverter circuit will be operated in buck mode with $S_2$, $S_3$ and $S_6$. $S_2$ and $S_3$ will switch simultaneously in high frequency, and $S_6$ remains on. The inverter operating mode is shown in Figure 4.11. As shown in Figure 4.11 (a), when $S_2$ and $S_3$ are turned on, $D_6$ will be turned off, and the energy will be transferred from dc to ac grid. As shown in Figure 4.11 (b), when $S_2$ and $S_3$ are turned off, the freewheeling current will go through $S_6$ and $D_6$. $S_2$ and $S_3$ are the active switches for buck conversion, $D_6$ is the freewheeling diode.

When the grid voltage is positive and the output current is negative, inverter works in region IV and the inverter circuit will be operated in boost
mode with \( S_6 \). Switch \( S_6 \) operates in high frequency, and \( D_2 \) and \( D_3 \) are the freewheeling diodes. The inverter operating mode is shown in Figure 4.12. As shown in Figure 4.12 (a), when \( S_6 \) is turned on, diodes \( D_2 \) and \( D_3 \) will be turned off, and the ac grid voltage will charge the filter inductor; as shown in Figure 4.12 (b), when \( S_6 \) is turned off, freewheeling current will go through diodes \( D_2 \) and \( D_3 \), and the energy will be transferred from ac side to dc side. The \( S_6 \) is the boost conversion active switch, \( D_2 \) and \( D_3 \) are the freewheeling diodes.

In summary, the improved inverter circuit can be operated in buck mode or boost mode to achieve any power factor operating, but a proper PWM modulation is need to operate this inverter circuit in these different modes for reactive power generation.

### 4.4 PWM method and realization for improved MOSFET inverter

As shown through Figure 4.12 to Figure 4.12, with a proper PWM modulation, the inverter can work in any power factor condition, but traditional unipolar modulation, bipolar modulation, and the modulation method proposed in [49] cannot be applied here. This section will propose a novel PWM realization method for reactive power generation and related implementation method. The control system for voltage reference generation is shown in Figure 4.13. As compared with the traditional H-bridge inverters, the control system and the sinusoidal voltage reference \( (V_{\text{ref}}) \) generation in the proposed inverter is as same as [96]-[98]. The difference is after getting the voltage reference \( (V_{\text{ref}}) \),
there will be individual duty cycle generator and individual PWM modulation for each switching device, which is shown in Figure 4.14.

![Control System Diagram](image)

**Figure 4.13** Control system for voltage reference generation

**Figure 4.14** Individual duty cycle generation and PWM modulation method

As shown in Figure 4.13, for a typical PV inverter, the control system should consist of an outer loop that regulates the dc input voltage and an inner loop that controls the ac output current. The outer loop controller regulates the dc voltage \( V_{dc} \) with a proportional-integral (PI) controller that provides the active current reference \( I_{d, ref} \). Through the phase-locked-loop (PLL), the phase angle information \((\sin \theta, \cos \theta)\) can be obtained through the grid voltage \( V_{ac} \). By
combining the active current reference and power factor command $\cos \phi$, a sinusoidal current reference $I_{\text{ref}}$ can be generated through the current reference generator module. Together with grid voltage feedforward control loop and the grid current feedback controller, a sinusoidal voltage reference ($V_{\text{ref}}$) can then be generated for duty cycle generation and PWM modulation.

As shown in Figure 4.14, proposed PWM method has an individual duty cycle generator and PWM modulation module for each pair of switches. The switches $S_1$ and $S_4$ obtain their duty cycle reference $d_{14}$ through a duty cycle generator ($S_1/S_4$), which will let inverter to be operated in buck mode in the I region (refer to Figure 4.14), and the duty cycle of the $S_1$ and $S_4$ is,

$$d_1 = d_4 = V_{\text{ref}}$$ (4.1)

The switches $S_5$ obtain the duty cycle reference $d_5$ through a duty cycle generator ($S_5$), which will let inverter to be operated in buck mode in the I region and the boost mode in the II region (refer to Figure 4.14). The $S_5$ will be constant on in I region, and the duty cycle of $S_5$ for the II region is:

$$d_5 = 1 + V_{\text{ref}}$$ (4.2)

The switches $S_2$ and $S_3$ obtain their duty cycle reference $d_{23}$ through a duty cycle generator ($S_2/S_3$), which will let inverter to be operated in buck mode in the III region (refer to Figure 4.14), and the duty cycle of $S_2$ and $S_3$ is:

$$d_2 = d_3 = -V_{\text{ref}}$$ (4.3)

The switches $S_6$ obtain the duty cycle reference $d_6$ through a duty cycle generator ($S_6$), which will let inverter to be operated in buck mode in the III
region and boost mode in the IV region (refer to Figure 4.14). The $S_6$ will be constant on in III region, and the duty cycle of $S_6$ for the IV region is:

$$d_6 = 1 - V_{ref}$$  \hspace{1cm} (4.4)

All four duty cycle generators can be easily realized in the PWM module of a digital signal processor (DSP), and their algorithms are described in Figure 4.14. After these duty cycle generators generate their duty cycle references ($d_{14}, d_5, d_{23}, d_6$), the PWM gating signals for each devices can be generated by comparing their duty cycle references with a triangular carrier $V_{carrier}$, as indicated in Figure 4.14.

![Image of Duty Cycle Generators](image)

Figure 4.15 Corresponding codes in DSP for duty cycle generator modules

The inverter system has been simulated with the proposed duty cycle generator and PWM modulation method described in Figure 4.13, Figure 4.13 and Figure 4.13.
Simulation results in Figure 4.13 shows the inverter output voltage, output current, gating signals: S₁/ S₄, S₅, S₂/ S₃, and S₆ for unity power factor condition.
Figure 4.17 Gating signals of $S_1/S_4$, $S_5$, $S_2/S_3$, and $S_6$ for current leading condition

Simulation results in Figure 4.13 shows the inverter output voltage, output current, gating signals: $S_1/S_4$, $S_5$, $S_2/S_3$, and $S_6$ for current leading condition.
Figure 4.13 Gating signals of $S_1$/ $S_4$, $S_5$, $S_2$/ $S_3$, and $S_6$ for current lagging condition.

Simulation results in Figure 4.13 shows the inverter output voltage, output current, gating signals: $S_1$/ $S_4$, $S_5$, $S_2$/ $S_3$, and $S_6$ for lagging conditions.

Figure 4.13 depicts the simulation results for the inverter operating under unity power factor condition with PF = 1. In this condition, the inverter output voltage and current follow the sequence of I $\rightarrow$ III, and only works in buck
operation in two different regions. The output PWM gating pattern for unity power factor condition is as same as the method presented in [26]. Figure 4.13 depicts the simulation results for the inverter operating under current leading condition with PF = −0.7. In this condition, the inverter voltage and current follow the sequence of I → IV → III → II. Figure 4.13 depicts the simulation results for the inverter operating under current lagging condition with PF = +0.7, inverter voltage and current will follow the sequence of IV → I → II → III.

4.5 Ground loop voltage analysis under reactive power generation

This Section will analyze the ground loop voltage of improved inverter under the proposed PWM modulation method. Analysis results will guide the circuit components design for low ground loop CM voltage.

![Figure 4.19 The inverter system with ground loop parasitic capacitor]

The equivalent circuit with CM and DM model in region I and III has been analyzed in [26], thus the following analysis will focus on the equivalent circuit in region II and IV.
When the inverter is operating in the region II, as shown in the Figure 4.10, the output terminals of the switch phase legs are $V_4$ and $V_1$, respectively. The equivalent circuit diagram with CM and DM representation in region II is shown in Figure 4.10.

When $S_5$ is turned on, as shown in Figure 4.10 (a), the CM and DM voltages are:

\[ V_{CM-II_{on}} = \frac{(V_4 + V_1)}{2} = \frac{V_{dc}}{2} \] (4.5)

\[ V_{DM-II_{on}} = V_4 - V_1 = 0 \] (4.6)

As shown in Figure 4.10 (b), when $S_5$ are turned off, the free-wheeling current goes through $D_1$ and $D_4$. The CM and DM voltages in the circuit are:

\[ V_{CM-II_{off}} = \frac{(V_4 + V_1)}{2} = \frac{V_{dc}}{2} \] (4.7)

\[ V_{DM-II_{off}} = V_4 - V_1 = V_{dc} \] (4.8)

So, when $S_5$ is turned on, as shown in Figure 4.10 (b), the ground loop voltage $V_{EG}$ is:
When $S_5$ is turned off, the ground loop voltage $V_{EG}$ is:

$$V_{EG-II\_off} = V_{CM-II\_off} + 0.5V_{DM-II\_off} - \frac{(V_{DM-II\_off} + V_{ac}) \cdot (L_{o3} + L_{o4})}{L_{o1} + L_{o2} + L_{o3} + L_{o4}}$$  \hspace{1cm} (4.10)$$

As shown in the Figure 4.10, when the inverter is working in the region IV, the equivalent circuit with CM and DM model in is shown in Figure 4.10.

When $S_6$ is turned on, as shown in Figure 4.10 (a), the ground loop voltage $V_{EG}$ is:

$$V_{EG-IV\_on} = V_{s\cdot G} + V_{E\cdot V_s} =$$

$$V_{CM-IV\_on} - 0.5V_{DM-IV\_on} + \frac{(V_{DM-IV\_on} - V_{ac}) \cdot L_{o3}}{L_{o1} + L_{o2} + L_{o3}} = V_{dc} \frac{V_{ac} \cdot L_{o3}}{2}$$  \hspace{1cm} (4.11)$$

When $S_6$ is turned off, as shown in Figure 4.10 (b), the ground loop voltage $V_{EG}$ is:
\[ V_{EG-IV_{-off}} = V_{CM-IV_{-off}} - 0.5V_{DM-IV_{-off}} + \frac{(V_{DM-IV_{-off}} - V_{ac}) \cdot L_{o3}}{L_{o2} + L_{o3}} \]
\[ = \frac{(V_{dc} - V_{ac}) \cdot L_{o3}}{L_{o2} + L_{o3}} \]  \hspace{1cm} (4.12)

In the inverter, if the inductances of \( L_{o2} \) and \( L_{o3} \) have the same value, and \( L_{o1} \) and \( L_{o4} \) values are equal, the ground loop voltage \( V_{EG} \) comes out to be the same in different operating modes according to analysis results in[49] and (3.9), (3.10), (3.11), and (3.12).

\[ V_{EG-I_{-on}} = V_{EG-I_{-off}} = V_{EG-II_{-on}} = V_{EG-II_{-off}} = \]
\[ V_{EG-III_{-on}} = V_{EG-III_{-off}} = V_{EG-IV_{-on}} = V_{EG-IV_{-off}} = \frac{V_{dc} - V_{ac}}{2} \]  \hspace{1cm} (4.13)

With proposed PWM modulation method, if the inductors (\( L_{o1} \) and \( L_{o4} \)) or inductors (\( L_{o2} \) and \( L_{o3} \)) are not designed to have similar inductance, the DM and CM voltages will have high-frequency components in the ground loop voltage \( V_{EG} \), which will result in high-frequency ground loop leakage current. In order to minimize this high frequency leakage current, \( L_{o2} \) and \( L_{o3} \) are better to be designed with same value. Similarly, \( L_{o1} \) and \( L_{o4} \) are also better to be designed with same value. With this inductor value match, the ground loop voltage \( V_{EG} \) will be a line-frequency sinusoidal voltage with a dc offset, which is shown in (19). In the hardware, \( L_{o2} \) and \( L_{o3} \) are coupled together, \( L_{o1} \) and \( L_{o4} \) are also coupled together, and the experimental waveform of \( V_{EG} \) will be shown in Section V to verify the validity of the analysis in this section.
4.6 Experimental results

The hardware experiments were conducted by using a 250 W two-stage micro-inverter [49], [50], [83]. Figure 4.10 shows the picture of the entire hardware prototype that consists of a dc-dc converter on the left-hand side and the proposed dc-ac inverter on the right-hand side. The dc-dc converter circuit is not the main focused on this paper but can be referred to [83].

The MOSFET inverter is running at 30 kHz; MOSFETs (S₁~S₆) are IPB65R190C7; diodes (D₁~D₆) are IDK03G65C5; inductors L₀₁ and L₀₄ are coupled together with 0.086 mH, inductors L₀₂ and L₀₃ are coupled together with 3.7 mH; filter capacitor Cᵉ is 0.47 uF [124-126].

Figure 4.22 250W micro-inverter hardware prototype
Figure 4.23 The PWM gating signals for unity power factor (PF=1) operation

Figure 4.24 The PWM gating signals for current leading (PF=-0.7) operation
Figure 4.25 The PWM gating signals for current lagging (PF=0.7) operation

With 30-kHz switching frequency, the PWM gating signals for unity power factor (PF=1) operation is shown in Figure 4.10; the PWM gating signals for current leading (PF=-0.7) operation is shown in Figure 4.10; the PWM gating signals for current lagging (PF=0.7) operation is shown in Figure 4.10. From the results, it can be seen that when the output voltage and current are both positive, S₁ and S₄ have the same high-frequency gating signal, while S₅ stays on with low-frequency switching. When the output voltage is negative and current is positive, S₅ will switch into high-frequency PWM operation. When the output voltage and current are both negative, S₂ and S₃ have the same high-frequency gating signal, while S₆ will stays on with low-frequency
operation. When the output voltage is positive, and the current is negative, $S_6$ will operate in high-frequency switching. With the proposed PWM modulation method described in Figure 4.10 and Figure 4.10, the experimental results (in Figure 4.10, Figure 4.10 and Figure 4.10) match the simulation results (in Figure 4.10, Figure 4.10, Figure 4.10) reasonably well.

![Figure 4.26 Voltage and current under PF=1](image)

Figure 4.26 Voltage and current under PF=1
Figure 4.27 Voltage and current under PF=0.7

Figure 4.27, Figure 4.26, and Figure 4.26 show output voltage, output current, and DC input voltage, under unity power factor (PF=1) operation, current lagging (PF=0.7) operation, and current leading (PF=-0.7) operation, respectively.

As shown in the Figure 4.22, the inductors (L_{o2} and L_{o3}) are coupled together, inductors (L_{o1} and L_{o4}) are also coupled together. As discussed in the section IV, if L_{o2} and L_{o3} are designed to have similar inductance, and L_{o1} and L_{o4} are designed to have similar inductance, the waveform of the ground loop voltage V_{EG}, which is between the ground of grid and the negative terminal of PV cells, should be a 60 Hz sinusoidal wave with a dc offset, which can be expressed in (3.13). The experiment waveforms in the Figure 4.22 clearly show that the ground loop voltage V_{EG} is a 60 Hz sinusoidal wave on top of a dc offset in both steady state and transient conditions.
The in-house measurement result of a commercial polycrystalline 240-W solar panel is around 0.6 nF. A 10 nF equalized parasitic capacitance is added into the ground loop for the worst case. The ground loop leakage current is shown in Figure 4.29, which indicates a less than 3 mA peak value. Therefore, with the proposed inverter circuit and the symmetrical design of inductors, the ground loop leakage current can be minimized by using the above proposed PWM modulation method.

![Figure 4.29 Ground loop leakage current waveform](image)

The inverter uses the CoolMOS IPB65R190C7 and SiC diode IDK03G65C5. YOKOGAWA WT1600 digital power meter is used to measure the voltages, currents, and efficiency of the proposed transformerless inverter (not including auxiliary power loss, DSP power losses, and first stage dc-dc converter). The efficiency measurement is based on measuring the inverter output ac power and the inverter dc input power. The CEC weighted efficiency of proposed inverter power stage, which is calculated at 10%, 20%, 30%, 50%, 75%, and 100%
of the rated power level, is 99.01%, and the efficiency profile is shown in Figure 4.30.

![Graph showing efficiency profile](image)

**Figure 4.30 Efficiency test results of proposed transformless inverter**

### 4.7 Summary

Reactive generation capability will be required for all the PV inverter for the upcoming new standards, but most of the state-of-the-art MOSFET transformerless inverters do not have reactive power capability, which is due to the MOSFET body diode reverse recovery issue. This chapter review all these MOSFET based transformerless inverters and summarized them into three types: (1) The High efficiency topologies suffer from MOSFET body diode reverse recovery for reactive power generation; (2) High efficiency MOSFET inverters don’t support reactive power generation, and also have low magnetic
utilization; (3) MOSFET inverter support reactive power generation, but have low efficiency and low magnetic utilization.

Based on the analysis of MOSFET inverter for reactive power generation, the high efficiency MOSFET based transformerless inverter in the Chapter 3 is introduced and improved for reactive power generation. The proposed inverter operating principle and PWM algorithm for reactive power generation are described in detail. The ground loop voltage is derived with common mode and differential mode circuit analysis using the proposed PWM method. The circuit analysis results indicate that the ground loop voltage will not contain high-frequency component by the symmetrical design of inductors. A 250-W micro-inverter hardware prototype has been designed and fabricated. Steady state and transient operating modes are tested to demonstrate the validity of proposed PWM method, the reactive power capability of proposed inverter, and the high-frequency component free of ground loop voltage. The power stage peak efficiency achieves 99.06% at 30-kHz operating frequency.
Chapter 5  Grid Connection Analysis and Design

5.1 Introduction

A typical grid-connected inverter system is shown in Figure 5.1, which have the voltage control unit, current control unit, phase-locked loop (PLL) unit, reactive power control unit, and the system monitor and protection unit [96-109].

Figure 5.1 Block diagram of a typical grid-connected inverter system

The current control and voltage control is the basic function of the grid-connected inverter, the modeling and control design will be present in the chapter 5.2.

The reactive power generation will be a basic function for the future PV inverter [10], [30]. The reactive power generation will shift from constant
power factor/ reactive power generation method to dynamic Volt-Var control method. The dynamic reactive power generation based on external command is presented in Chapter 5.3.

The PLL not only need for the current loop control and voltage loop control, but also required for the system monitor and protection. Traditional PLL method doesn’t have enough accuracy for the frequency and voltage magnitude detection [97], [105], [106], Chapter 5.4 will present an improved PLL method for fast frequency and voltage magnitude detection.

5.2 System control and modeling

![Block diagram of a simplified control system](image)

Figure 5.2 Block diagram of a simplified control system

For the voltage control and current control system, the simplified control block diagram is shown in the Figure 5.2. The dc bus control is the outside control loop, the ac current control is the inside control loop. The control output of the dc bus control will be the current reference for the active component, the
PLL unit will provide the angle/phase information for the active and reactive current control. $G_{cv}(s)$ is the dc bus voltage controller; $G_{cj}(s)$ is the ac current controller; $K_f(s)$ is the feedforward controller; $H_i(s)$ is the current sensor loop filter [98-99].

5.2.1 Current loop modeling and control

For the current control loop, the simplified control system is shown in Figure 5.3, $F_m$ is the digital system, which include the PWM modular; $G_{id}(s)$ is the transfer function from controlled duty cycle to filter inductor ac current; $G_{vi}(s)$ is the transfer function from the ac grid voltage to the filter inductor ac current [100-103].

![Simplified current control system](image)

Figure 5.3 Simplified current control system

For the current sensor, there is a second-order filter $H_i(s)$, and the transfer function is,

$$H_i(s) \approx \frac{1}{1 + \frac{2\xi}{\omega_i}s + \frac{s^2}{\omega_i^2}}$$  \hspace{1cm} (5.1)
Where, $\omega_i$ is the second-order cut off frequency at 10 kHz, and $\xi$ is damping factor, which is 0.7 in this paper. The bode diagram of this low-pass filter is shown in Figure 5.4.

![Bode Diagram](image)

**Figure 5.4** Bode diagram of second-order low-pass filter

As the simplified function of the inverter is an amplifier, so the transfer function from the duty $d$ to inverter side inductor current $I_{ac}$, which is presented as $G_{id}(s)$, can be expressed as:

$$G_{id}(s) \approx \frac{V_{dc}}{sL_i + R_i} \quad (5.2)$$

The bode diagram of $G_{id}(s)$ the is shown in Figure 5.5, which shows 90 degree phase delay for the frequency is higher than 300 Hz.
For the inverter, as the simplified function is like an amplifier, so there is a block for signals normalization. For the digital control system, there is a time delay from the sampling, calculation, and the final PWM gating. All these digital delays which is close to one PWM switching cycle in this paper. $F_m(s)$ is an simplified block to present the signals normalization and digital control system delay effect. The simplified transfer function of $F_m(s)$ is:

$$ F_m(s) = \frac{1}{V_{dc}} \cdot e^{-sT_s} \approx \frac{1}{V_{dc}} \cdot \frac{1 - sT_s}{2} \frac{2}{1 + sT_s} $$  \hspace{1cm} (5.3) $$

The bode diagram of the $F_m(s)$ is shown in Figure 5.6, which shows the constant gain and increasing phase shift from digital delay.
$G_{vi}(s)$ presents the transfer function from grid ac voltage to filter inductor ac current, the transfer function can be expressed as:

$$G_{vi}(s) \equiv \frac{1}{sL_i + R_i} \quad (5.4)$$

The purpose of the feedforward control of grid ac voltage is to use the ac voltage information to cancel the effect of the grid ac voltage on the filter inductor current [103]. For the feedforward control loop, the transfer function from the grid ac voltage to the inductor current is:

$$G_{vi_{ff}}(s) = K_{ff}(s) \cdot F_m'(s) \cdot G_{id}(s) \quad (5.5)$$

Due to this feedforward control is especially for the line frequency ac voltage, so the PWM digital delay in the $F_m'(s)$ can be ignored, so as long as the
\( K_{ff}(s) \) can achieve proper gain for the line frequency ac voltage, the grid ac voltage on filter inductor ac current effect can be canceled under the condition of:

\[
G_{vi_{ff}}(s) = G_{vi}(s)
\]  

(5.6)

With the feedforward control, the grid ac voltage on filter inductor ac current effect can be canceled, so the current control loop can be simplified as a single loop negative feedback control system, which is shown in Figure 5.7.

![Figure 5.7 Simplified current control system with feedforward control](image_url)

With the simplification of the feedforward control, the open loop transfer function without current controller in Figure 5.7 (or the current control loop plant \( G_{\text{open-di}}(s) \)) is:

\[
G_{\text{open-di}}(s) = F_m(s) G_{id}(s) H_i(s)
\]  

(5.7)

The bode diagram of the current control loop plant \( G_{\text{open-di}}(s) \) is shown in the Figure 5.8.

For the current control, the proportional resonant (PR) controller is adopted to minimize the 60 Hz steady-state error [104], the transfer function is

\[
G_{e_{-rl}}(s) = k_p + \frac{2k_{rl} \omega_{c1}s}{s^2 + 2\omega_{c1}s + \omega_o^2}
\]  

(5.8)
Where, the $k_p$ is the proportional parameter, $k_{r1}$ s gain parameter of the resonant controller, which is designed to allow high gain at the 60 Hz and $\omega_{c1}$ is selected to ensure enough phase margin and implementation realization.

In order to achieve lower harmonics low distortion for the grid current, multiple resonant controllers are added together [104], so the final transfer function of the current controller is:

$$G_{c-i}(s) = k_p + \frac{2k_{r1}\omega_{c1}s}{s^2 + 2\omega_{c1}s + \omega_o^2} + \sum_{h=3,5,7,9,11,13,15} \frac{2k_{rh}\omega_{ch}s}{s^2 + 2\omega_{ch}s + (h\omega_o)^2} \tag{5.9}$$

The bode diagram of the current controller $G_{c-i}(s)$ is shown in Figure 5.9. As shown in the Figure 5.9, the resonant controllers are designed until 15th harmonic, which means, the control bandwidth will be higher than 900 Hz.
Figure 5.9  Bode diagram of current controller $G_{c,j}(s)$

With the current controller, the open loop transfer function of the current control loop is:

$$G_{open,j}(s) = F_m(s)G_{id,j}(s)H_1(s)G_{c,j}(s)$$  \hspace{1cm} (5.10)
The bode diagram of the current loop with controller is shown in Figure 5.10, the bandwidth is 1160 Hz, the phase margin is 55.4 degree, and the gain margin is 12 dB. The multiple PR controller has infinite gain at each harmonics [104].

![Bode Diagram](image)

Figure 5.11  Bode diagram of current control close loop $G_{close_{-}ii}(s)$

With the current controller, the close loop transfer function of the current loop is:

$$G_{close_{-}ii}(s) = \frac{F_m(s)G_{sd}(s)G_{c_{-}i}(s)}{1+F_m(s)G_{sd}(s)H_i(s)G_{c_{-}i}(s)}$$  \hspace{1cm} (5.11)

The bode diagram of the close loop transfer function $G_{close_{-}ii}(s)$ is shown in Figure 5.11, which shows the output can almost follow the input for 1000 Hz bandwidth.
5.2.2 DC voltage loop modeling and control

The current control loop has high bandwidth and is the inner loop, the voltage control loop has very narrow bandwidth and is the outside loop. The bandwidth of the current control loop is more than ten times higher than the voltage controller loop, so each control loop can be designed independently. For the voltage control loop, the 120Hz is a naturally result from the power coupling, so it should be out of the dc voltage control loop bandwidth.

For the PV application, the dc PV power source can be modeled as a current source $I_{PV}$. The input and output energy relationship under steady state can be expressed as:

$$I_{PV}V_{dc} = V_{ac} \cdot I_{ac} \quad (5.12)$$

Under small disturbance theory, the relationship between the ac current and dc voltage can be expressed as:

$$I_{PV}(V_{dc} + \hat{v}_{dc}) - V_{dc}C_{dc} \frac{d(V_{dc} + \hat{v}_{dc})}{dt} = V_{ac} \cdot (I_{ac} + \hat{I}_{ac}) \quad (5.13)$$

The relationship between ac current disturbance and the dc voltage disturbance is:

$$I_{PV} v_{dc} - V_{dc}C_{dc} \frac{d \hat{v}_{dc}}{dt} = V_{ac} \hat{I}_{ac} \quad (5.14)$$

So, the transfer function from ac current to dc voltage is:

$$G_{i_{ac} \rightarrow V_{dc}}(s) = \frac{V_{dc}}{I_{ac}} = \frac{V_{ac}}{I_{PV} - sV_{dc}C_{dc}} \quad (5.15)$$
The simplified dc bus control system is shown in Figure 5.12.

$$G_{open_{iv}}(s) = -G_{i_{ac}}(s) \cdot G_{close_{ii}}(s)$$ (5.16)

The bode diagram and the Nyquist plot of this transfer function $G_{open_{iv}}(s)$ is shown in Figure 5.13 and Figure 5.14 respectively.
The dc voltage controller is PI controller, the transfer function of PI controller is:

\[ G_{c,v}(s) = K_p \frac{K}{s} + K_i \frac{1}{s} \]  \hspace{1cm} \text{(5.17)}

The open loop transfer function of the voltage loop without controller is:

\[ G_{\text{open}_{-vv}}(s) = -G_{i\text{-ac}}(s) \cdot G_{\text{close}_{-ii}}(s) \cdot G_{c,v}(s) \]  \hspace{1cm} \text{(5.18)}

The bode diagram of the voltage loop open loop transfer function \( G_{\text{open}_{-vv}}(s) \) is shown in Figure 5.15, which shows 44.6 Hz bandwidth and 60.2 degree phase margin.
Figure 5.15  Bode diagram of voltage control open loop $G_{\text{open,vv}}(s)$

Figure 5.16  Nyquist plot of voltage control open loop $G_{\text{open,vv}}(s)$ for wide frequency range
The Nyquist plot of the voltage loop open loop transfer function $G_{open,vv}(s)$ is shown in Figure 5.16 with wide frequency range view. The Figure 5.16 shows the Nyquist plot for the low frequency view, which shows the plot will counterclockwise surround the $(-1,0)$. So the control system is stable with right half plan pole of the $G_{open,vv}(s)$.

![Nyquist Diagram](image)

**Figure 5.17** Nyquist plot of voltage control open loop $G_{open,vv}(s)$ for low frequency range

The DC bus control on the inverter is show in Figure 5.18. the dynamic response shows the DC is control from 370 to 400 Vdc. The Figure 5.19 shows the steady-state waveform of the dc bus voltage, ac voltage, and the ac current.
Figure 5.18 DC bus voltage is control from 370 to 400 Vdc

Figure 5.19 the steady state waveform for ac current/voltage and dc voltage

5.3 Dynamic reactive power generation

As discussed in the Chapter 4.1, all the PV inverters need have reactive power generation capability to meet upcoming standards. IEEE 1547a permit setting the power factor of a PV inverter to be a static value, but it does not permit dynamic voltage operation. The dynamic reactive power generation/compensation is also called dynamic voltage operation, which allow
distribution power system to counteract voltage deviation from the nominal voltage level by consuming or producing reactive power. The purpose of reactive power generation/compensation is used to help power grid to maintain voltage levels with the system normal ranges. The difference between the constant power factor running and the dynamic reactive power generation is that the inverter can actively regulate the voltage at the point of common coupling (PCC) [107-109].

Traditional reactive power generation methods usually are based on an established “curve” which define the voltage versus the percentage of reactive power. The percentage of reactive power can be calculated as:

1. Percentage of available reactive power for the measured percentage of the reference voltage. “Available Vars” implies the consumption or production of reactive power that does not affect the real power output.

2. Percentage of maximum reactive power. In this case, consumption or production of reactive power may affect the real power output.

The curve of the Voltage-Var control with dead-band method is shown in Figure 5.20, which use a dead-band between $V_2$ and $V_3$ around the nominal voltage[107-108].

The curve of the Voltage-Var control with hysteresis method is shown in Figure 5.21, which use a hysteresis to dampen the unnecessary swings for the boundary condition.
The dynamic voltage var control in this paper is not based on the predefined curse, the reactive power generation command is superseded by the external signals issued by the area power system operator. So all the PV inverter can be control by a centralized controller to do reactive power generation. So each inverter only need to know the power factor command from the centralized power system controller. But this means the inverter need to have the communication capability, such as network bridge method, or wireless method, such as Bluetooth, ZigBee, Power Line communication, WiFi method. This work use the wireless communication system which is based on a wireless
signal communication module (NRF24L01+). The overall block diagram for the dynamic Voltage-Var control is shown in Figure 5.22 [107-109].

![System block diagram of Voltage-Var control](image)

Figure 5.22  System block diagram of Voltage-Var control

If the power factor (PF) command information is received from the centralized power system controller, together with the active current reference from the dc bus voltage control and the phase information from the PLL, the final reference current will be:

$$I_{ac}^* = I_{ac_{-P_m}} \sin \omega t + \frac{\sqrt{1 - PF^2}}{PF} I_{ac_{-P_m}} \cos \omega t$$  \hspace{1cm} (5.19)

The reactive power generation dynamic response is shown in Figure 5.23 and Figure 5.24 respectively. The Figure 5.23 shows the voltage and current waveforms under transition from unity power factor (PF=1) operation to current lagging (PF=0.7) operation. The inverter dc bus voltage is 380V, and
the ac grid voltage is 240V. Before the transition, the inverter is operating under 250-W pure active power condition, and the output voltage and output current are in phase. After the transition, the inverter is operating under current lagging (PF=0.7) condition, and the ac output power is about 350 VA, which includes 250 W active power and 250 VAR overexcited reactive power.

Figure 5.23 shows the transition from unity power factor (PF=1) to current leading (PF=0.7) operation. Before the transient, the inverter is also working under 250-W pure active power condition. After the transient, the inverter is operating under current leading (PF=0.7) condition, the ac output power is about 350 VA, which consists of 250W active power and 250 VAR under-excited reactive power.

![Diagram](image)

**Figure 5.23** Transient form unity power factor (PF=1) operation to reactive power generation (PF=0.7) operation
All the dynamic reactive power generation process in the Figure 5.23 and Figure 5.24 shows the fast transient.

5.4 A novel PLL for grid voltage/frequency disturbance

5.4.1 Traditional PLL method

For the grid connected inverter system, a phase-locked loop (PLL) is an essential part for getting the correct grid voltage phase/angle information, frequency information, and voltage magnitude information. For the traditional grid-connected inverter system, the PLL is mainly design to the correct phase/angle information to inject a related synchronizing ac current into the grid [105·106]. The PLL is a closed-loop system to let the output sinusoid waveform to follow the input sinusoid waveform. The traditional PLL block for grid synchronization is shown in Figure 5.25, which consists of three blocks:
The phase detector block: this block use the input signal and feedback output signal to achieve a feedback control system. The input signal is $V_{\text{grid}}$, the feedback signal of output is $V_f$, the multiplier of these two signals is the $V_e$.

The loop controller block: the basic function of this block is to adjust the error signal to let the output signal $V_{\text{syn}}$ follow the input signal $V_{\text{grid}}$. When the phase of output signal $V_{\text{syn}}$ just follow the input signal $V_{\text{grid}}$ phase angle, the $V_f$ and $V_{\text{grid}}$ will have 90 degree phase shit, the output $V_e$ will be a pure sinusoids waveform, after the low pass filter, the $\Delta \omega$ will be zero. The bandwidth of the low pass filter should be much lower than the double line frequency.

The voltage-controlled oscillator. This block will change the frequency information in to a time domain sinusoids waveform. Due to the input signal is dc, the output signal is sinusoid waveform, so its function like an oscillator.

With this traditional PLL method, the $V_{\text{syn}}$ can catch the phase of $V_{\text{grid}}$ very well, which is demonstrated in Figure 5.26.
For the grid-connected inverter, PLL not only need to know the phase information, but also need know the frequency information to handle the frequency disturbance. The frequency information in the Figure 5.25 is $\omega_0$, the simulation result of is show in Figure 5.27, which shown the frequency detection results has significant double line frequency. This double line frequency signal in the frequency will make it is impossible for the inverter to detection the frequency range between 59.3 Hz and 60.5 Hz.
5.4.2 Improved PLL method

The main issue for the inaccurate frequency detection in the traditional PLL is the double line frequency. In order to minimize the effect of this double line frequency on the frequency detection, this paper proposed a improve PLL method, which is shown in Figure 5.28. the overall structure of the PLL module is almost the same, the only difference is a notch filter (NF) is added behind the low pass filter. The NF is based on the 90 degree phase shift unit (PSU), the equation of the 90 degree phase shift unit is:

$$PSU = \frac{\omega_{2c} - s}{\omega_{2c} + s}$$  \hspace{1cm} (5.20)

Due to the notch filter is used to filter the double line frequency, so $\omega_{2c}$ should be:

$$\omega_{2c} = 2 \cdot \omega_c = 240\pi$$  \hspace{1cm} (5.21)

The block diagram of the notch filter (NF) is shown in Figure 5.29, and the equalized equation is:

$$NF = \frac{s^2 + \omega_{2c}^2}{s^2 + 2s\omega_{2c} + \omega_{2c}^2}$$  \hspace{1cm} (5.22)
The simulation result of improved PLL is shown in Figure 5.27, which shows the frequency detection accuracy has been significantly improved. The result in the Figure 5.27 shows that this a ± 2 Hz error. The simulation result in Figure 5.30 shows that the error is within ± 0.1 Hz. The frequency detection response is less than three cycles after a step change, which can meet the standards requirement for 10 cycle’s response.

![Notch Filter](image)

**Figure 5.29** The block diagram of notch filter

![Frequency Detection](image)

**Figure 5.30** Frequency detection results of improved PLL.

Proposed improved PLL method is realized in the digital signal processor, the experimental results for abnormal frequency condition are shown in the Figure 5.31 and the Figure 5.32. As shown in the Figure 5.31, the grid voltage (yellow curve) frequency is jumped from 60 Hz to 60.5 Hz, the real frequency information (or the frequency reference) is shown with the blue curve, the
measured PLL frequency is the red curve, which shows the frequency detection can be achieved in three line cycle.

Figure 5.31 Experimental abnormal over-frequency trip.

As show in the Figure 5.32, the grid voltage (yellow curve) frequency is jumped from 60 Hz to 59.3 Hz, the real frequency information (or the frequency reference) is show with the blue curve, the measured PLL frequency is the red curve, which shows the frequency detection can be achieved in four line cycles.

This improved PLL for the abnormal frequency disturbance is also test in the inverter system. For the over-frequency test, the frequency is jumped from
60.0 Hz to 60.5 Hz, the inverter detect the frequency change, and shut down the system within 0.08 S, as shown in Figure 5.33.

For the under-frequency test, the frequency is jumped from 60.0 Hz 59.3 Hz, the inverter detect the frequency change, and shut down the system within 0.084 S, as shown in Figure 5.33.

Figure 5.33  Abnormal over-frequency test

Figure 5.34  Abnormal under-frequency test
### Table 5.1 Summary of abnormal frequency test results

<table>
<thead>
<tr>
<th>Frequency range (Hz)</th>
<th>Disconnection Time (s)</th>
<th>IEEE 1547</th>
<th>Inverter Test Result</th>
</tr>
</thead>
<tbody>
<tr>
<td>$f &gt; 60.5$</td>
<td>0.16</td>
<td>0.0</td>
<td>0.084</td>
</tr>
<tr>
<td>$f &lt; 59.3$</td>
<td></td>
<td></td>
<td></td>
</tr>
</tbody>
</table>

#### 5.4.3 Voltage magnitude detection method

The grid voltage magnitude is an important information for power calculation, voltage protection. For the grid-connected PV inverter, another importance of the voltage magnitude detection is for the voltage disturbance reaction. Under different under voltage or over voltage condition, the inverter need to stay with normal connection or disconnection within specified time [105-109].

The voltage magnitude detection method in this paper is also based on the 90 degree phase shit unit, this phase shift unit is design for the line frequency, so the transfer function is:

$$PSU_1 = \frac{\omega_c - s}{\omega_c + s}$$  \hspace{1cm} (5.23)

The voltage magnitude detection is shown in Figure 5.35.

![Voltage magnitude detection method](image.png)

*Figure 5.35  Voltage magnitude detection method*
With the above voltage magnitude detection method, the Figure 5.36 shows the 88% under-voltage test results. The inverter trips at 1.6 s, which is within the 2-s standard’s limit.

Figure 5.36  Under-voltage (88%) test result.

Figure 5.37 shows the 50% under-voltage test results. The inverter trips at 0.08 s, which is within the 0.16-s standard’s limit.

Figure 5.37  Under-voltage (50%) test result.
Figure 5.38 and Figure 5.39 show the over-voltage test results under 110% and 120% over-voltage conditions. The inverter trips at 0.64 and 0.11 s, respectively. Both trip times are within the standard's limits of 1-s and 0.16-s, respectively.

Table 5-2 summarized the comparison with the IEEE 1547 standards for the abnormal voltage disturbance. With the above voltage magnitude calculation,
the voltage detection, the trip time in all can be programmed to meet the standard’s requirement.

Table 5-2 Summary of abnormal voltage test results

<table>
<thead>
<tr>
<th>Voltage range (%)</th>
<th>Disconnection Time (s)</th>
</tr>
</thead>
<tbody>
<tr>
<td></td>
<td>IEEE 1547</td>
</tr>
<tr>
<td>V &lt; 50</td>
<td>0.16</td>
</tr>
<tr>
<td>50 ≤ V &lt; 88</td>
<td>2.00</td>
</tr>
<tr>
<td>110 &lt; V &lt; 120</td>
<td>1.00</td>
</tr>
<tr>
<td>V ≥ 120</td>
<td>0.16</td>
</tr>
</tbody>
</table>

5.5 Summary

Besides the high efficiency inverter circuit topology, the inverter control and grid connection functions are also the essential part of the PV system. This chapter present the inverter grid connection system and each block’s function.

Based on the system characteristic, this current and voltage control is model and design. The modeling and design of control take considering of the feedforward control, digital delay, the uncoupling of two control loop. The overall system modeling and design present a simple and effect way for grid-connected converter system control and design.

In order to realize the dynamic reactive power control for the future grid requirement, a dynamic reactive power control system is realized based on the wireless communication method. The dynamic reactive power control performance is verified with experiment.

The inverter reaction to abnormal grid is also discussed in this chapter. The traditional PLL is good for current control system, but the accuracy is not
enough for the grid frequency disturbance detection and protection. This chapter proposed an improved PLL, which can improve the accuracy significantly to meet the standard requirement for the frequency disturbance. A similar method is also adopted into the voltage magnitude detection method. Experimental results demonstrate the validity of the proposed method for grid disturbance detection and protection.
Chapter 6 Conclusions and Future Work

6.1 Conclusions

Power electronic converter is the heart of every PV plant, which is an environmentally power generation system that uses the PV cells to convert sunlight into electrical power. High efficiency is preferred for maxim solar energy extraction, high reliable/low cost/low volume inverter design, and fast custom investment return. State-of-the-art transformerless inverter can reached around 97% efficiency. Some special transformerless inverter topology can achieve more than 98% efficiency.

This dissertation viewed the state-of-the-art transformerless inverter high efficiency topologies and summarized a new inverter technology. With this new inverter technology, a family of high efficiency transformerless inverters are proposed. The proposed inverters not only demonstrate the summarized new inverter technology, but also offer a high efficiency and patent free solutions.

Most of the innovative transformerless inverter topologies MOSFET to boost efficiency. However, these MOSFET based inverter topologies suffer from one or more of these drawbacks: MOSFET failure risk from body diode reverse recovery, increased conduction losses due to more devices, or low magnetics utilization. With a brief review of these MOSFET based transformerless inverters, a novel MOSFET based phase-leg method is proposed. With this proposed MOSFET phase-leg, a high efficiency MOSFET based
transformerless inverter is proposed. The experimental results of this MOSFET based inverter not only demonstrate the validity of the proposed MOSFET phase-leg method for high efficiency, high magnetic utilization, and low risk from MOSFET body diode, but also provide a new way to build other high efficiency transformerless inverters.

Due to the reactive power generation will be required for all the PV inverters, and most of the state-of-the-art high efficiency MOSFET based transformerless inverter don’t have reactive power generation capability. This work improve the proposed high efficiency MOSFET transformerless inverter, and a novel PWM is proposed for the reactive power generation. Experimental result demonstrate the validity of this improve transformerless inverter and the reactive power generation capability.

Besides the high efficiency inverter circuit, the grid connection function is also the essential part of the PV system. The current control and voltage control loop is analyzed, model, and designed. The dynamic reactive power generation is also realized in the control system. The new PLL method for the grid frequency/voltage disturbance is also realized and demonstrate the validity of the detection and protection capability for the voltage/frequency disturbance.

The work in this research has resulted in the following contributions:

1. Based the review of the state-of-the-art transformerless inverter topologies, a new inverter technology is summarized. The new inverter
technology is named as Neutral Point Virtually Clamped (V-NPC) inverter topology.

2. With the principle of V-NPC inverter technology, a family high efficiency transformerless inverters are proposed. A 250 W hardware prototype is designed and tested to demonstrate the low common mode voltage and 98.96% peak efficiency. The ground loop voltage analysis method is also presented, which is based on the CM and DM model.

3. A novel MOSFET based phase-leg is proposed for high efficiency inverters. Based on the this proposed MOSFET phase-leg, a 99.06% peak efficiency MOSFET based transformerless inverter is proposed, which also has high magnetic utilization and avoid the MOSFET body diode reverse recovery.

4. A novel PWM method is proposed for the reactive power generation of proposed MOSFET inverter.

5. Current loop and voltage loop model have been both derived and designed. The dynamic reactive power generation is also realized in the control system. The new PLL method for the grid frequency/voltage disturbance is also realized and demonstrate the validity of the detection and protection capability for the voltage/frequency disturbance.

6.2 Future work

The research work in this dissertation demonstrates promising performance in high efficiency transformerless inverter circuit, using
MOSFET to replace the IGBT in the high efficiency transformerless inverter, realized reactive power generation with MOSFET based transformerless inverter, and high performance for grid connection function. However, there are other areas where further investigations will be required to increase the overall performance of the system efficiency and function capability. The following topics are recommended for future work.

• **Device package**

  In the proposed high efficiency MOSFET based transformerless inverter system, there are a lot discrete power devices. For the power circuit, the high efficiency means high frequency and high power density. So with proper device package, such as all the discrete power devices are packaged in one module, the overall size can be minimized, the parasitic can be also minimized for higher efficiency.

• **New inverter circuit with V-NPC method**

  With the review of state-of-the-art transformerless inverters, the V-NPC method is summarized, and a family of high efficiency transformerless inverter is proposed. New inverter circuit can be derived through this V-NPC method, which will be an interesting topic for future research.

• **New power electronics circuit with proposed MOSFET phase-leg**

  With the review of state-of-the-art MSOFET based transformerless inverters, the MOSFET based phase-leg method is summarized, and a high efficiency transformerless MOSFET inverter is proposed and verified. This
MOSFET phase-leg method not only can be applied in to transformreless inverter topology, but also can be applied to most of the phase-leg that want adopted high voltage MOSFET. New power electronics circuit can be derived through this proposed MOSFET based phase-leg, which will be an interesting topic for future research.

- **Effect of reactive power generation on system cost and efficiency**

  The reactive power generation is realized on the proposed high efficiency MOSFET based transformerless inverter. But the effects of the reactive power generation on the cost and efficiency have never been discussed, which will be a very practical research topic.

- **Standard compliance**

  New standard also requires the low voltage ride through, which is not done in this work. Besides, more work need to be done for the inverter to pass the UL1741.

**List of publications**

Different parts of this work have already been published or are being published in international journals or conference proceedings. These publications are listed below.


164


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